

Status of the tests on the 8x32 3DTC chips and preliminary results of the 2012 beam test on *INMAPS*

beam test on *INMAPS*

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INFN - Sezione di Pisa

and the 2012 testbeam team

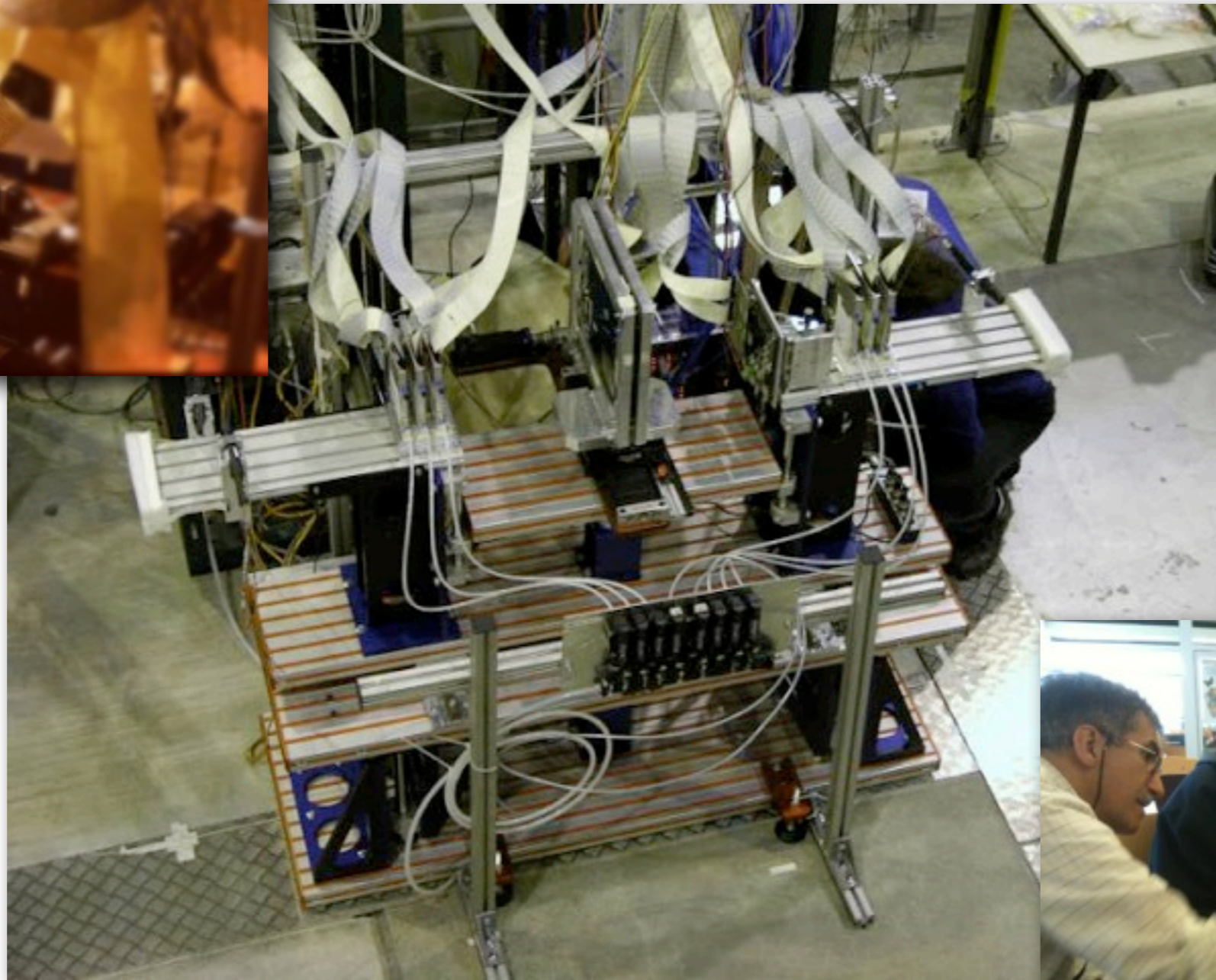
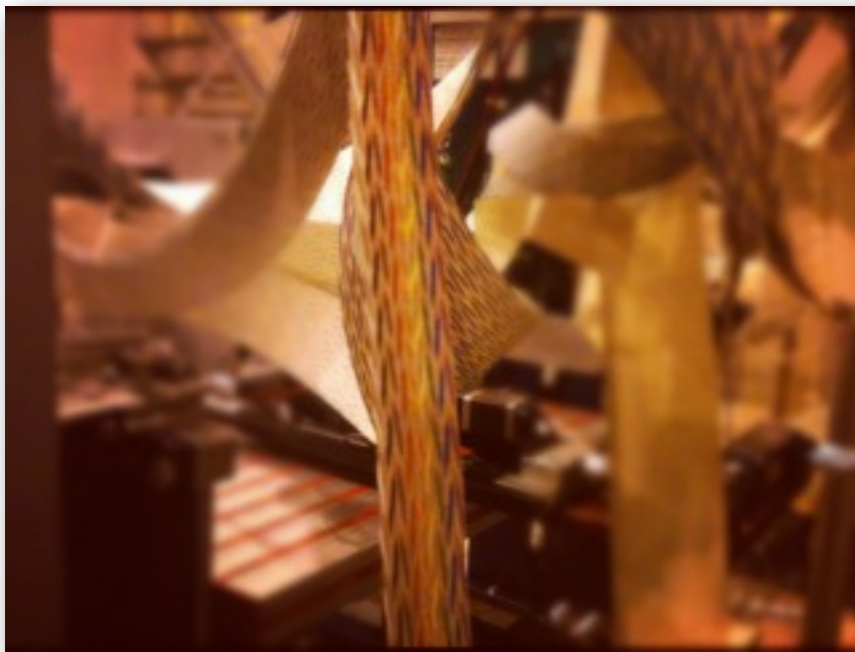
PRIN 2009 / VIPIX Meeting - Milano

outline

- ➔ CMOS MAPS in 180 nm INMAPS technology: *Apsel4Well*
 - testbeam results, efficiency vs threshold
 - results of the lab tests on inductions

- ➔ Vertically Integrated DNW MAPS: *Apsel3D_TC*
 - lab characterizations
 - interconnection of the two layers
 - tests on inductions

NOTE: signal amplitudes in mV are *not corrected* for the buffer scaling factor (0.9)



Apse4Well

Apse4Well reminder

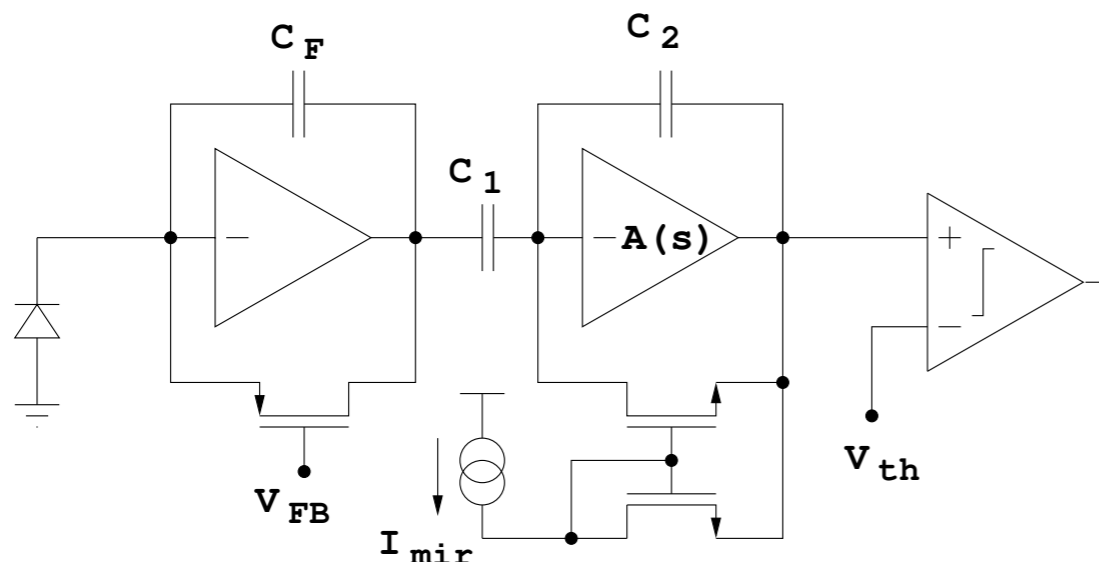
- ➔ 32x32 matrix organized in 2x8 macropixels (MP)
 - can mask selected MPs
 - data-push & triggered readout architecture
- ➔ 3x3 analog-only chips
- ➔ thickness: 5 and 12 μm
- ➔ resistivity: standard (10 Ωcm) and high (1 $\text{k}\Omega\text{cm}$)

12 μm - high Ω	DAC	mV ^(*)	e ⁻
thr. disp.	34	10	80
noise	17	5.1	42
gain (mV/fC)	860 ^(*,c) (diff. spectr. ⁵⁵ Fe)		
gain disp.	5%		
MIP	-	115.5	930
⁵⁵ Fe peak	-	203 ^(c)	1640
S/N	22		

(*)corrected for buffer scaling factor (0.9)

(c)central pixel (chip42)

- ➔ block diagram of the pixel analog front-end:



- shaping with a current mirror in the feedback network (V_{rifmir} adjusts discharge time and gain)
- analog output available for pixel (31,31)
- can inject a charge only in pixel 31,31
- the signal is *negative*

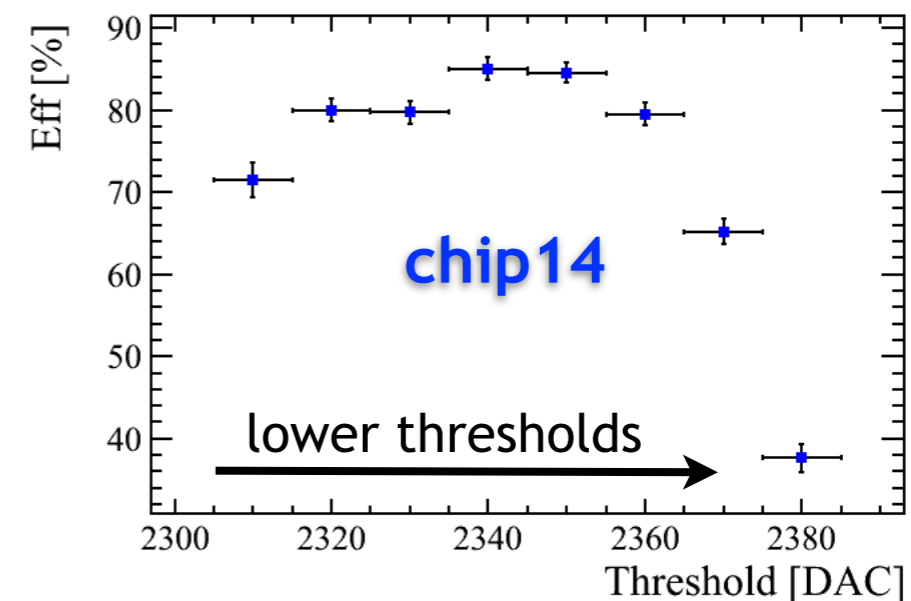
Apse14Well on beam

- ➔ analog INMAPS and 3 chips 32x32, (hi Ω , 12 μ m) have been tested with a 120 GeV/c pion beam
 - analog INMPAS results not available yet
 - preliminary results available for digital chips:
 - efficiency vs threshold (DAC)
 - efficiency vs angle
 - resolution
 - resolution vs angle
 - lattice & pixel isotropy (still convolved with telescope resolution)

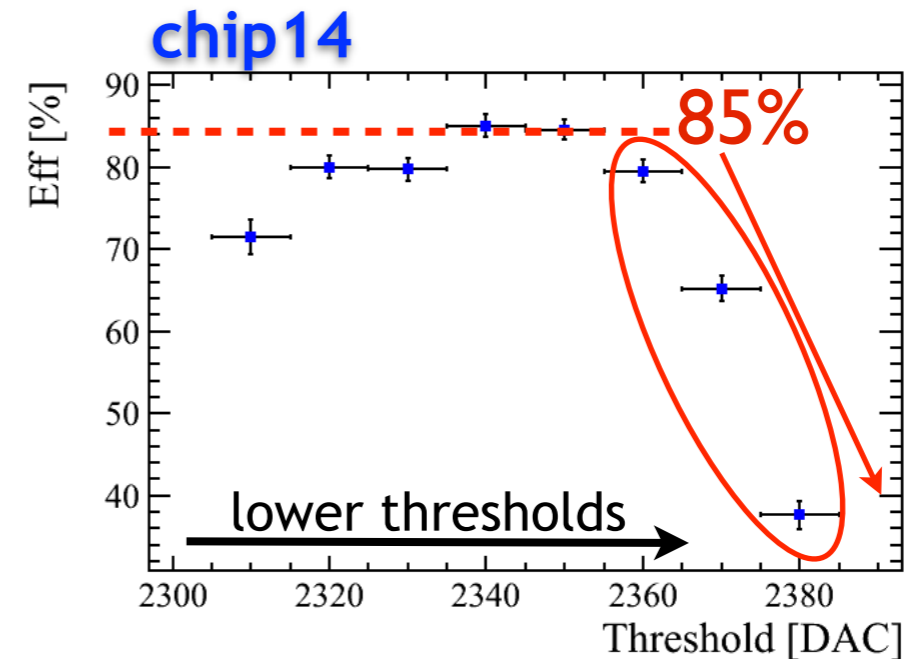
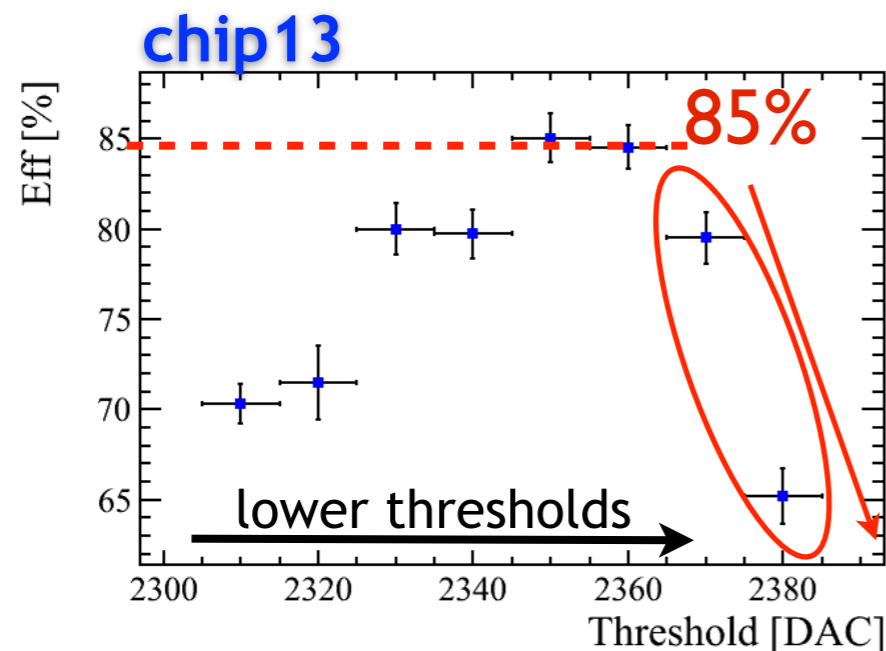
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- ➔ The main issue with this chips is related to the low maximum efficiency reached and its deterioration at low thresholds:

- current explanation: inductions effects



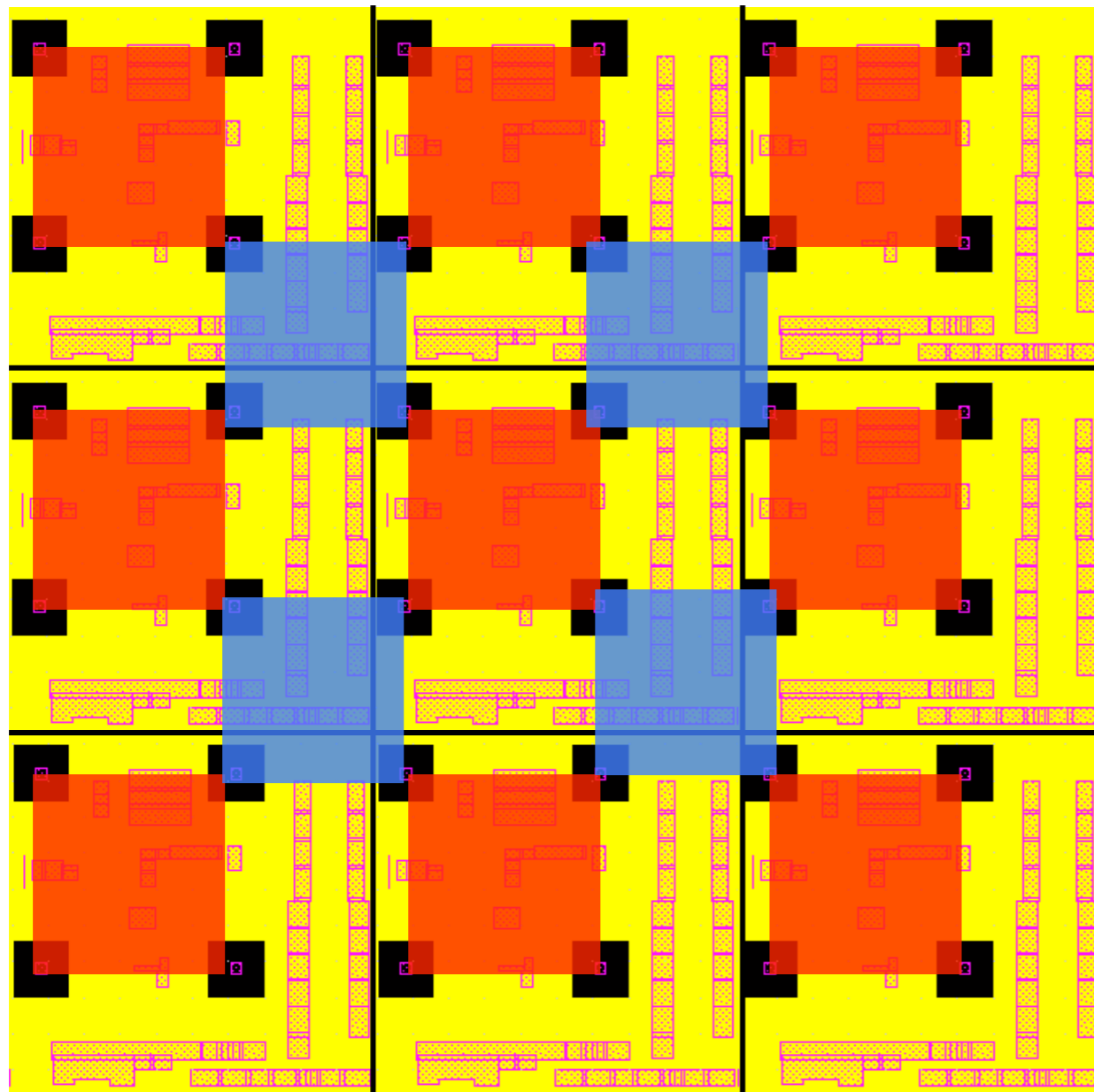
Efficiency vs Threshold



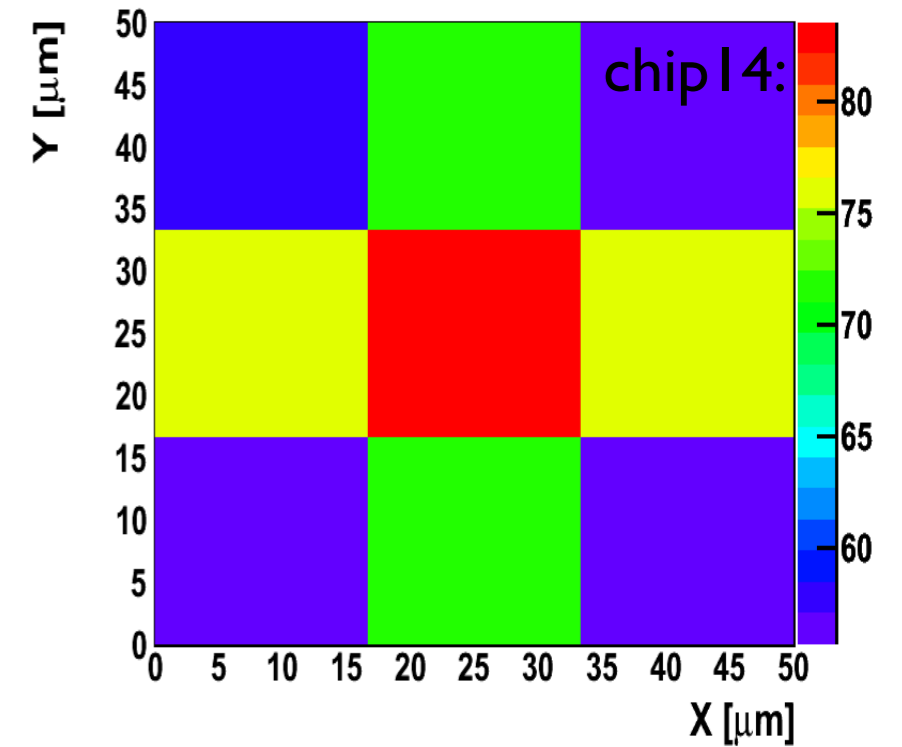
- ➔ $\epsilon_{\max} \sim 85\%$ (@ 2360 DAC $\sim 300e^-$), deterioration at lower thresholds.
- ➔ possible answers:
 - inefficiency due to the fact that the pixel is already fired (on noise, or other...): excluded (v. bkp slide 20)
 - inefficiency due to **induction effects** (positive induction related to digital activity masks negative signal from particles)
 - *other effects* that may be related to the low maximum efficiency: charge sharing (v. next slide and 27) and too high threshold (v. bkp slide 28)

Efficiency Within Pixel

- ➔ Low efficiency regions: the released charge is shared among more than 1 pixel and not enough to go below threshold.

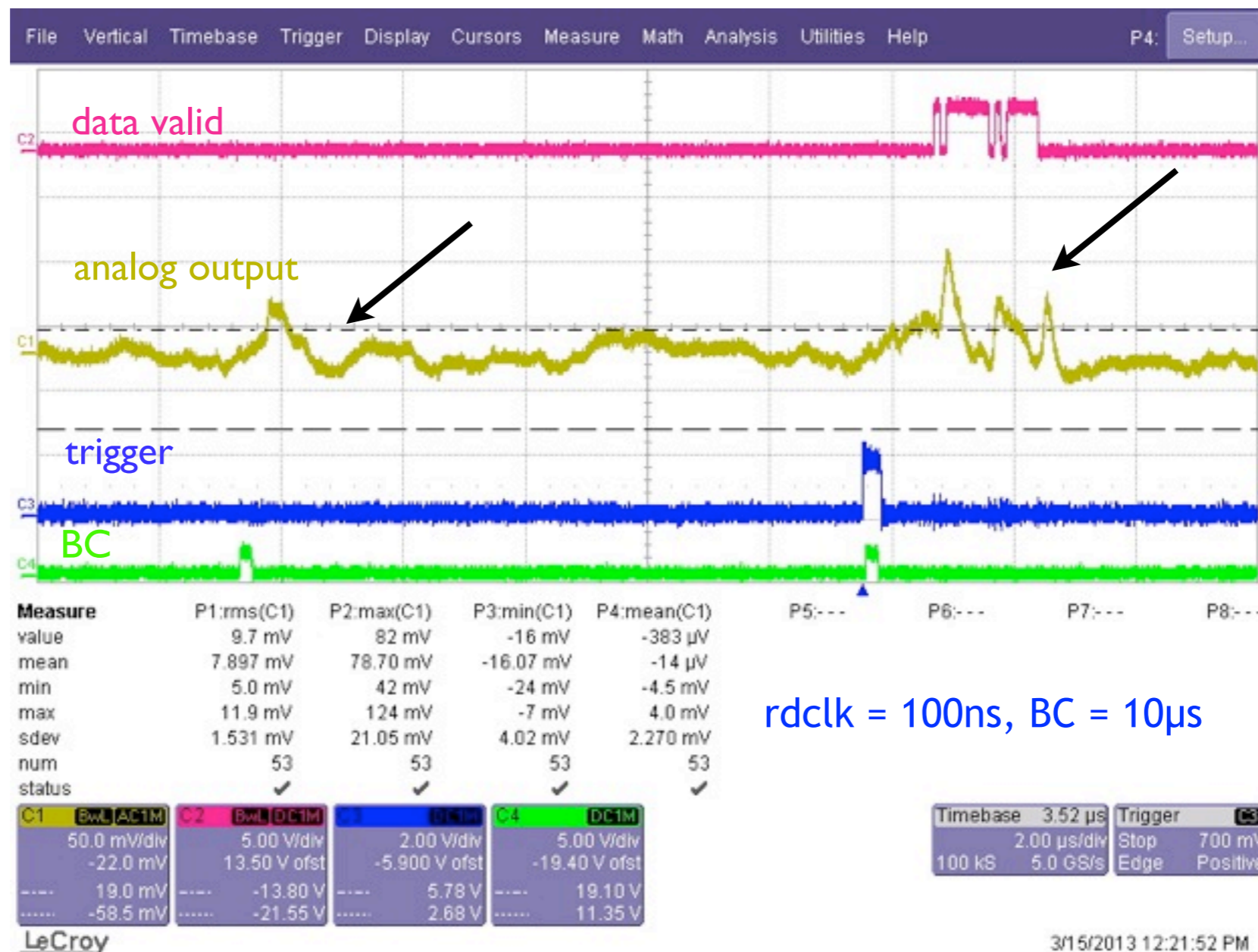


in-pixel efficiency (still convolved with telescope efficiency):



Induction Effect #1

1. When a timestamp or a hit is readout we observe **big positive spikes** on the analog output (50 - 100mV). Also in correspondence of some BCs, signals going towards the matrix (TS update) induce **positive and negative spikes**



2 μ s

50mV

MIP \approx 115 mV

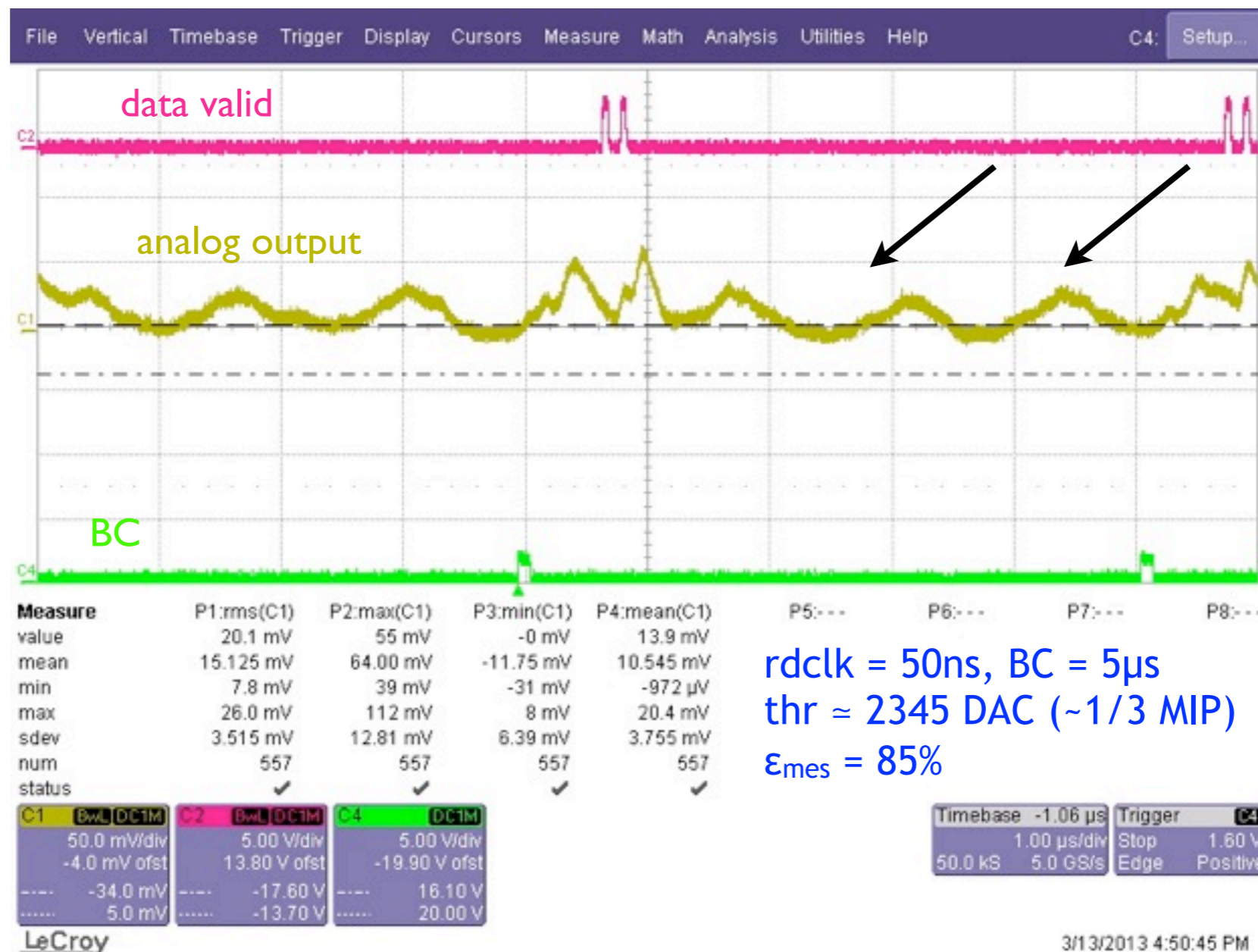
rdclk = 100ns, BC = 10 μ s

Timebase 3.52 μ s
 2.00 μ s/div
 100 kS 5.0 GS/s
 Trigger C3
 Stop 700 mV
 Edge Positive

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Inductions Effect #2

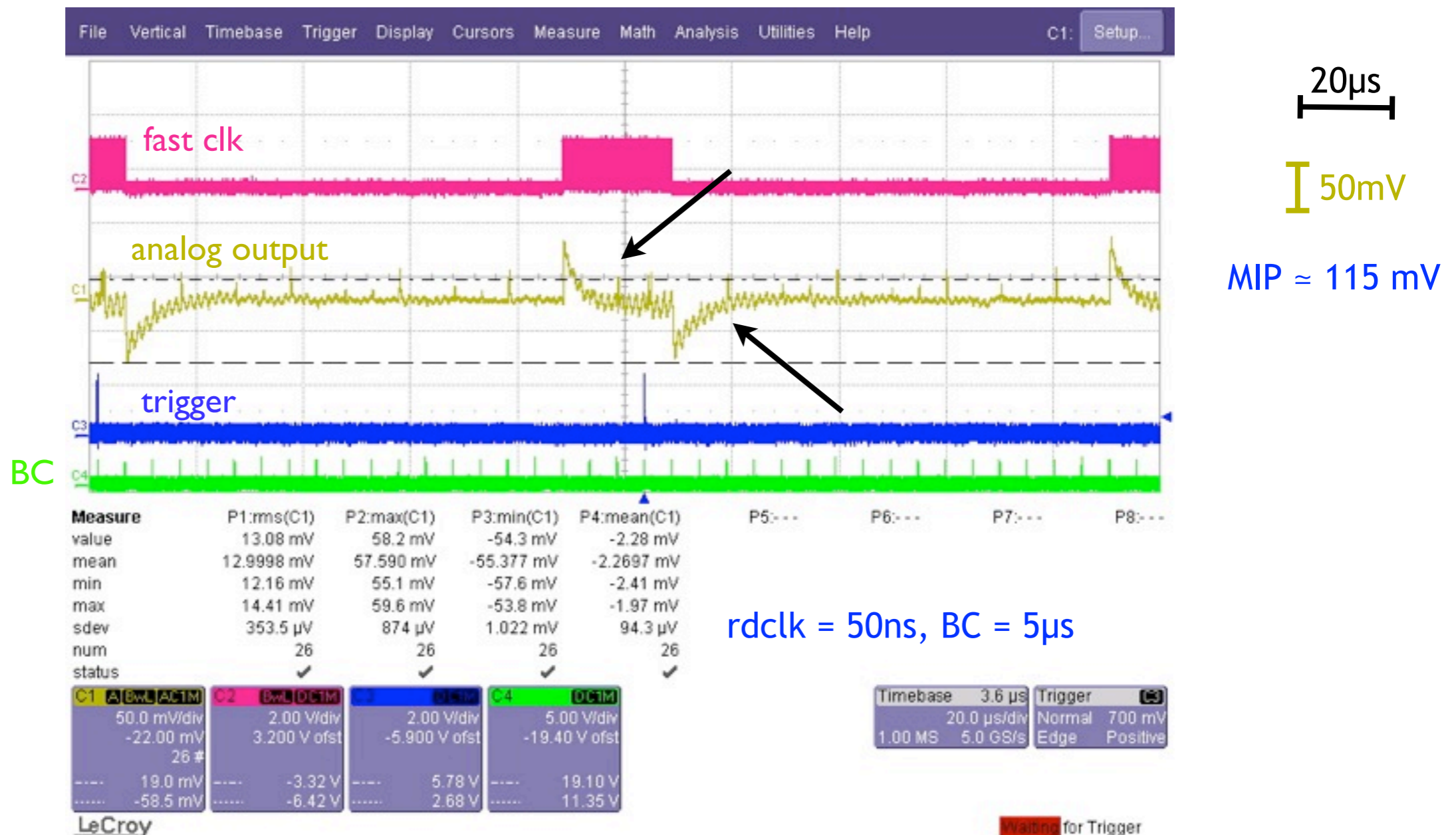
2. When rdclk/fastclk > 20MHz (50ns) we observe an **oscillation** independent of the BC period present only if fastclk is active (due to activity in the periphery).



1 μs
 50 mV
 MIP ≈ 115 mV

Induction Effect #3

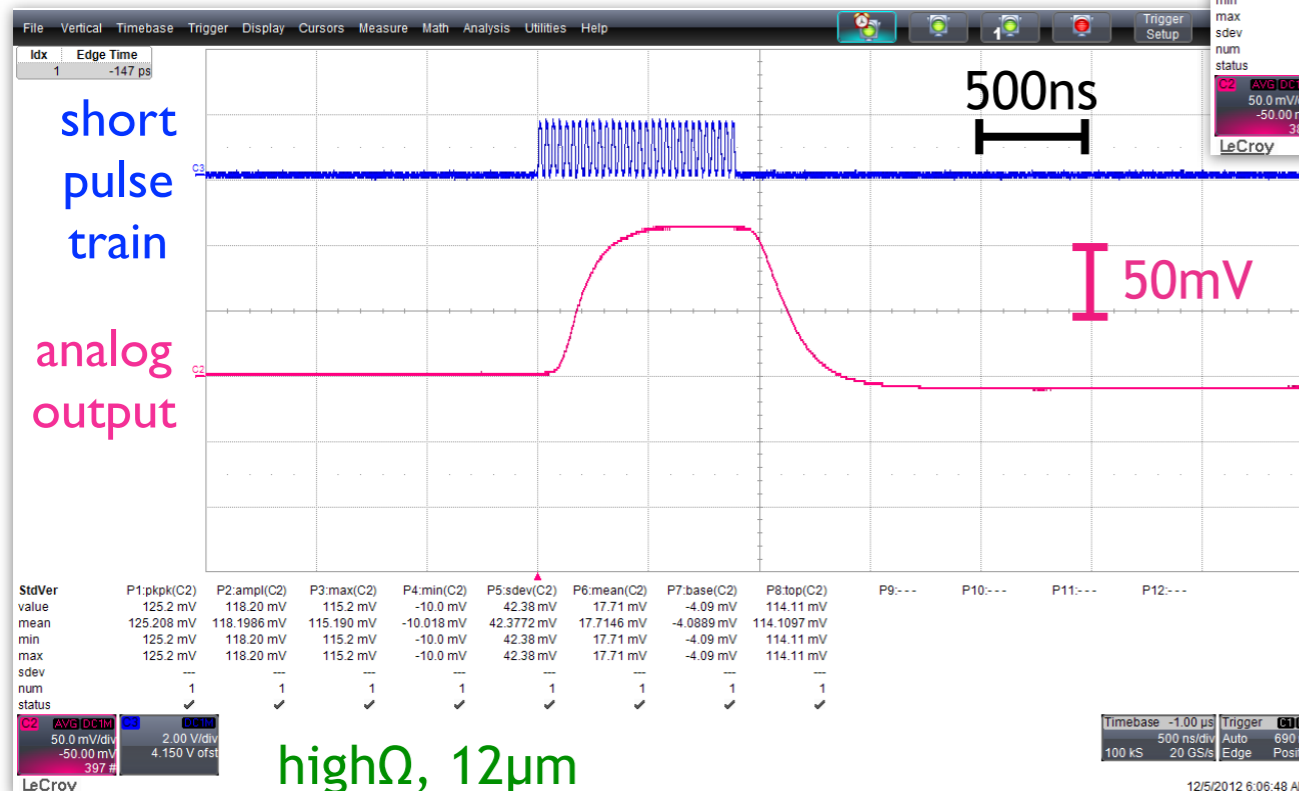
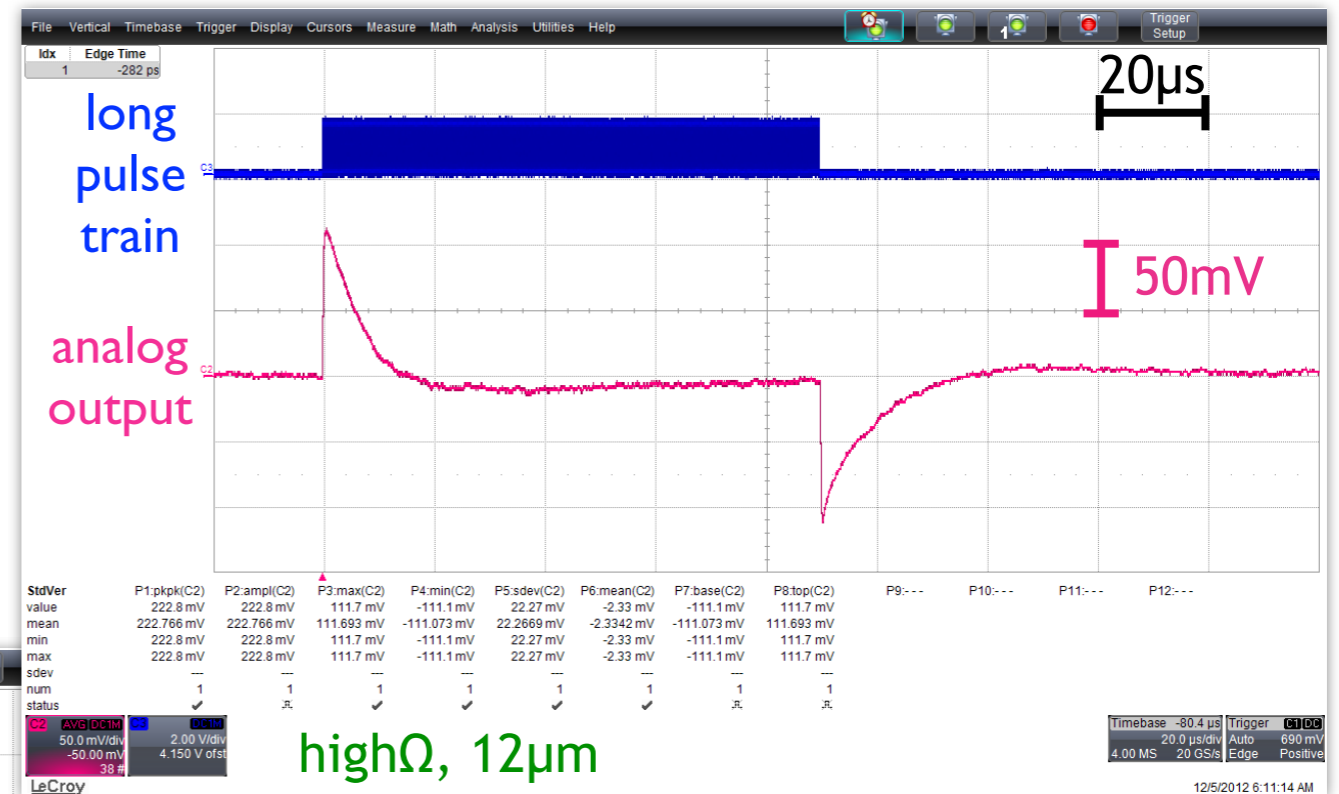
3. We observe **big (50 - 100 mV) positive (negative) spikes** when fastclk starts (ends) in the periphery. The superimposed **oscillation** is present only if fastclk > 20MHz and is attenuated in $\sim 30 \mu\text{s}$.



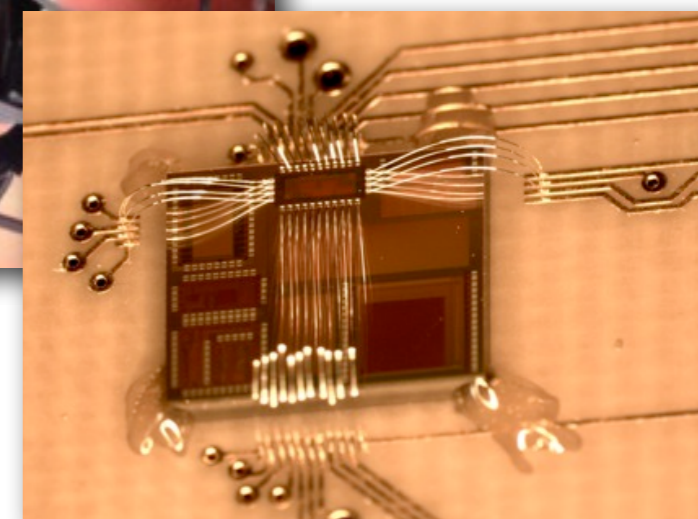
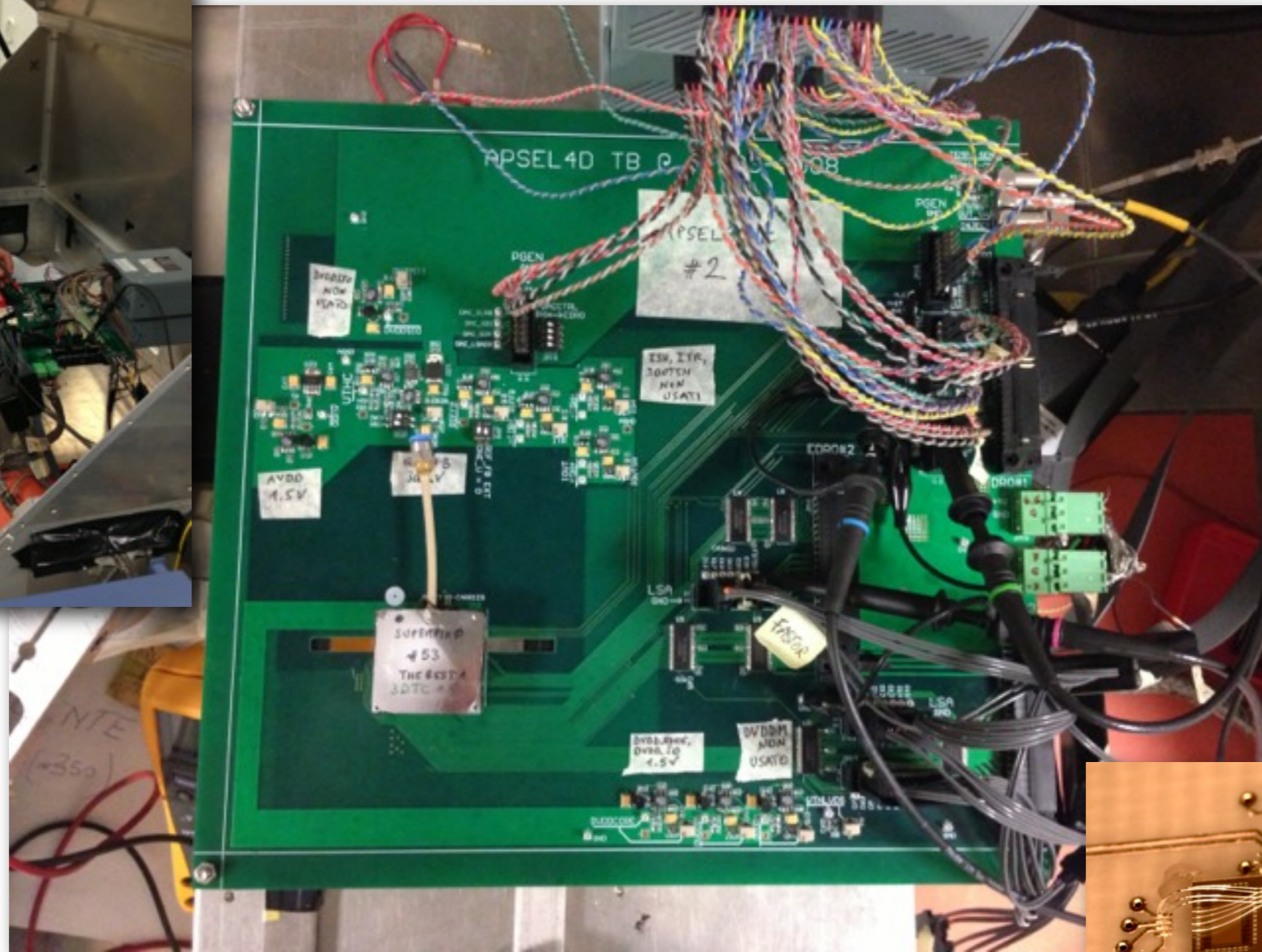
Tests on Analog 3x3 Matrices

→ Tests on a 3x3 analog matrix show similar effects when digital signals run on the chip.

- ▶ positive pulse triggered by the start of the train and sensitive to the frequency of pulses
- ▶ negative pulse, same amplitude as the positive one, triggered by the interruption of the pulses
- ▶ when train is shorter, the two pulses merge



1. maximum effect obtained with pulse train period of 25 - 30 ns
2. level of induction is ~proportional to the amplitude of the pulse train
3. the effect is independent of the stimulated track
4. the effect in some lowΩ chips seems smaller



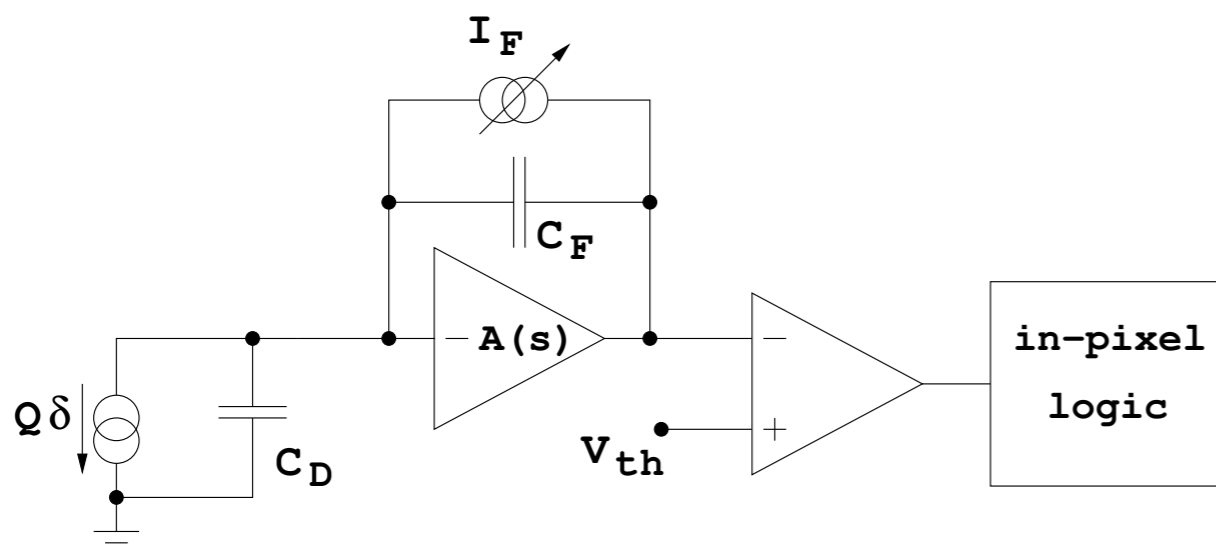
Apse13D_TC

Apse13D_TC reminder

- ➔ 8x32 matrix organized in 4x4 macropixels (MP)
 - can mask selected MPs
 - data-push readout architecture
- ➔ 3x3 analog-tier only chips

	DAC	mV	e-
thr disp	11-14	3.4 - 4.3	80 - 90
noise	5.4 - 6.2	1.7 - 1.9	40
gain (mV/fC)	290 (digital)	320 (analog)	
gain disp.	20%		
MIP	-	40	1000
⁵⁵ Fe peak	-	80	
S/N	23		

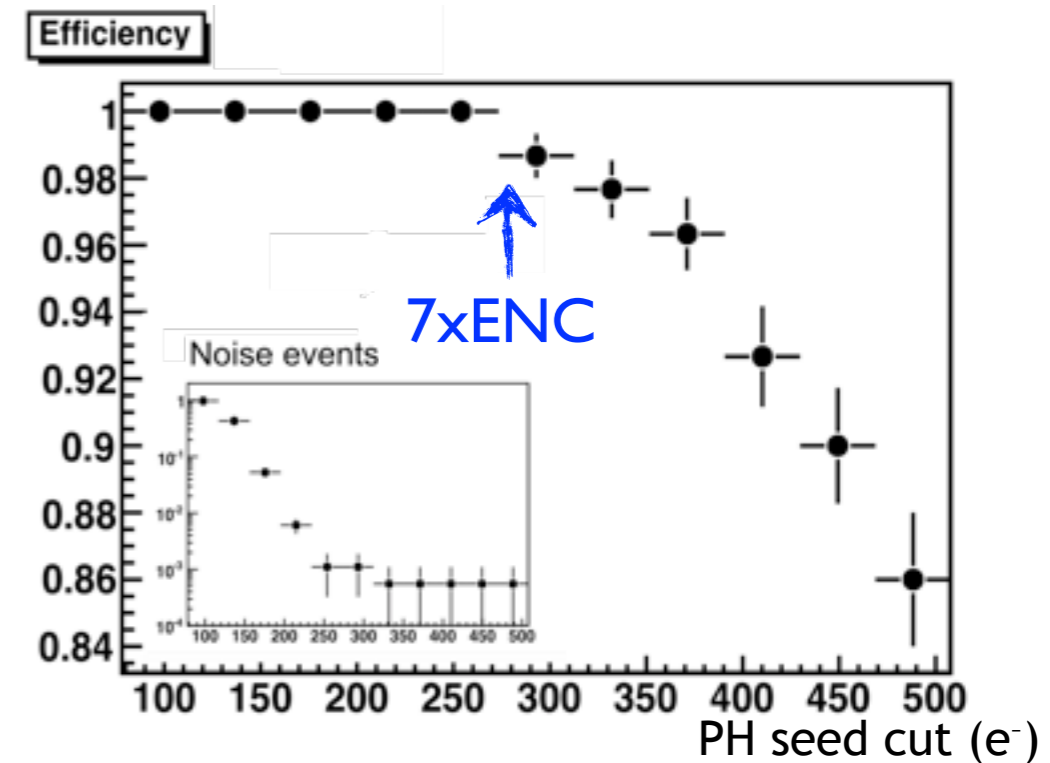
- ➔ block diagram of the pixel analog front-end:



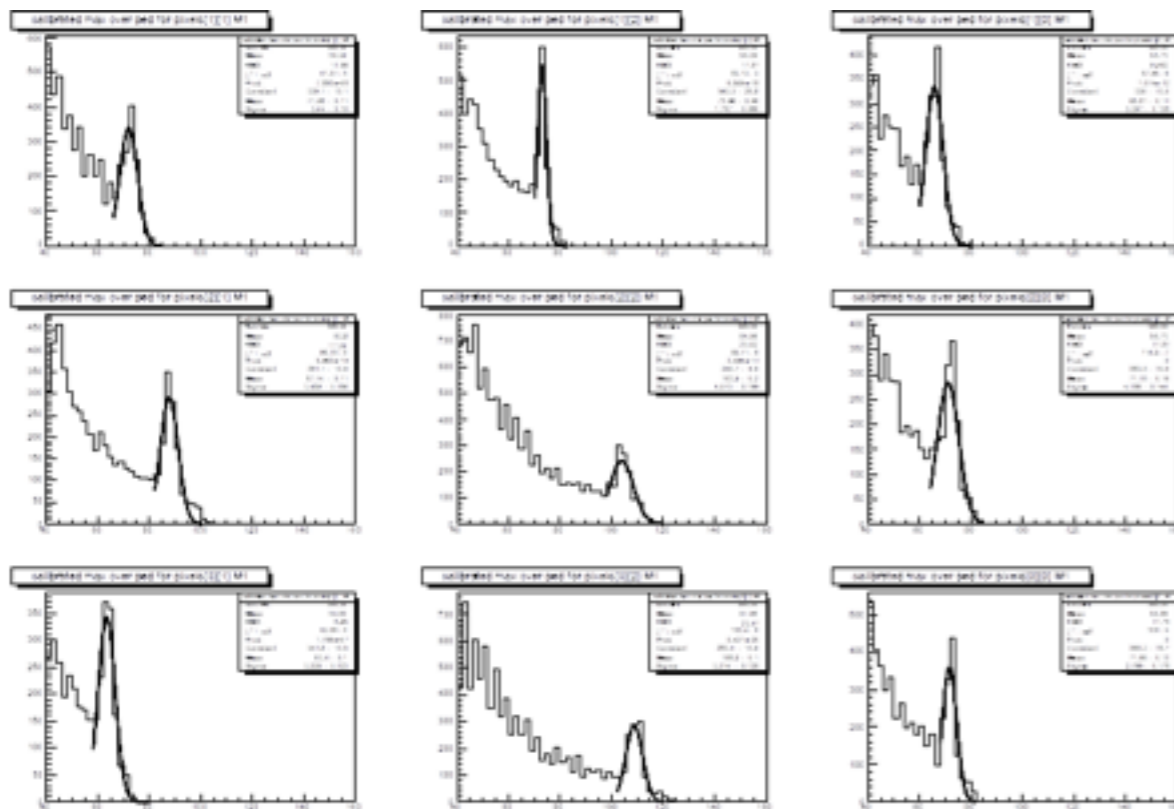
- bandwidth-limited preamplifier to improve signal-to-noise
- analog output available for pixel (31,7)
- can not inject a charge
- the signal is *positive*

Apse13D_TC - analog-tier only

- ➔ tested on beam (2011):
 - 3x3 cluster signal MPV $\approx 1000 e^-$
 - $S/N \approx 23$
 - efficiency $\approx 98\%$ at thresholds up to 7xENC



differential spectrum of the 3x3 pixels (⁵⁵Fe):



- ➔ tested with a ⁵⁵Fe source:
 - 5.9 keV γ , 1640 e⁻ $\approx 2xMIP$
 - measured gain ≈ 320 mV/fC (half the expected value) and quite dispersed
 - feedback capacitance of the preamplifier realized exploiting parasitic capacitance of two tracks
 - value estimated from post-layout simulations: not reliable (\rightarrow low gain) and quite dispersed (\rightarrow dispersed gain)

Apse13D_TC calibrations

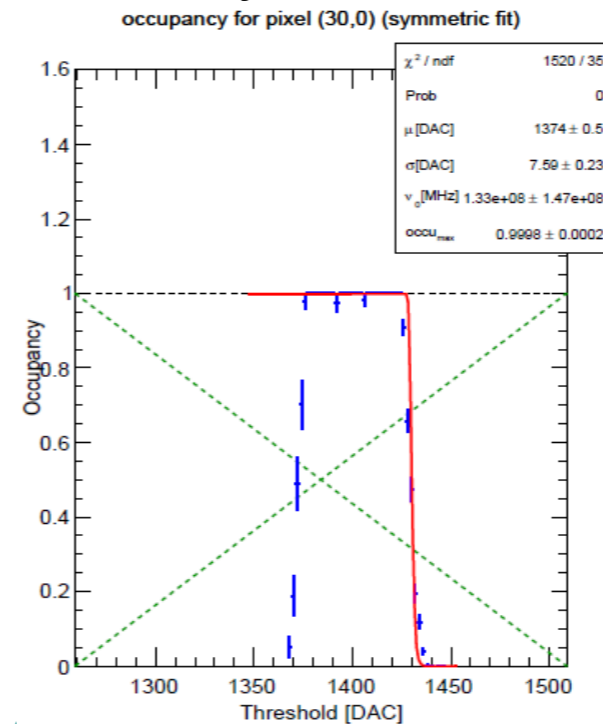
➔ Noise Scans:

- ▶ need to fit with *asymmetric* function

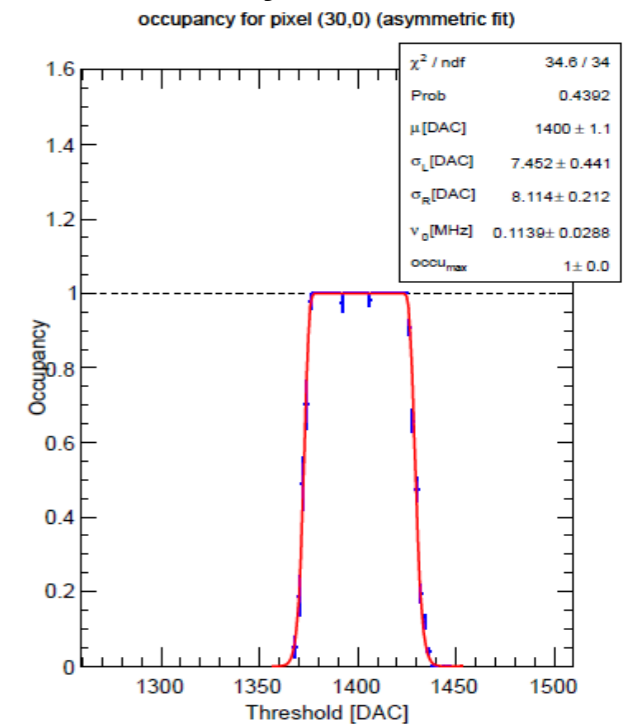
something asymmetric in the circuit? comparator?

- $\sigma_L \approx 85\% \sigma_R$, $\sigma_R \approx 1.7 - 1.9$ mV
- $\sigma_R \sim$ in agreement with what seen on the analog output of pixel (31,7)
- ▶ limited threshold dispersion
 - 3.4 - 4.2 mV ($\sim 2.5 \times \sigma_R$)

Symmetric fit

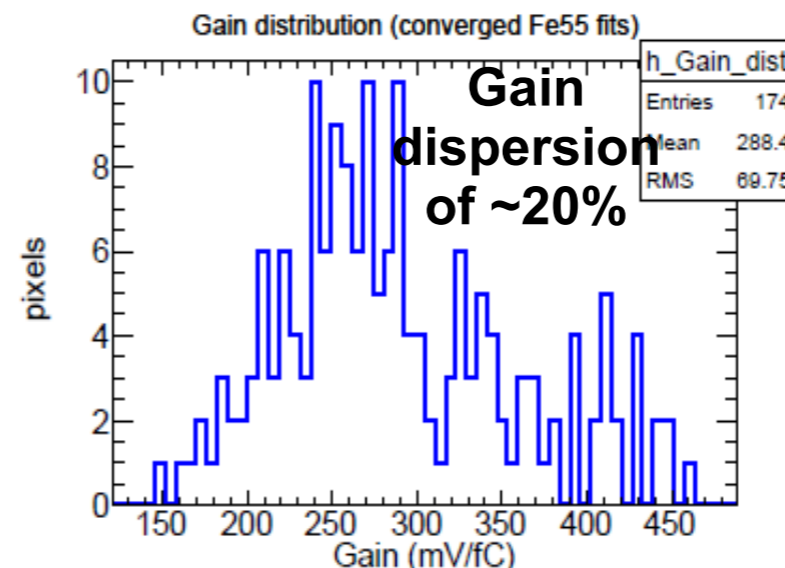
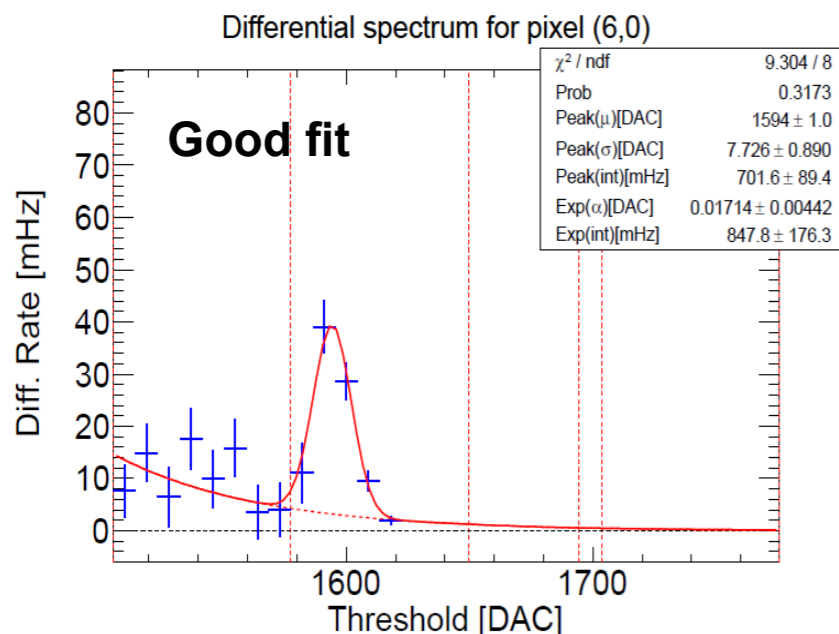


Asymmetric fit



➔ Gain Calibrations with ^{55}Fe ($1640 e^- \approx 2 \times \text{MIP}$), differentiated digital scan:

- ▶ central value ≈ 285 mV/fC, very large dispersion, $\approx 20\%$ (even within a MP)

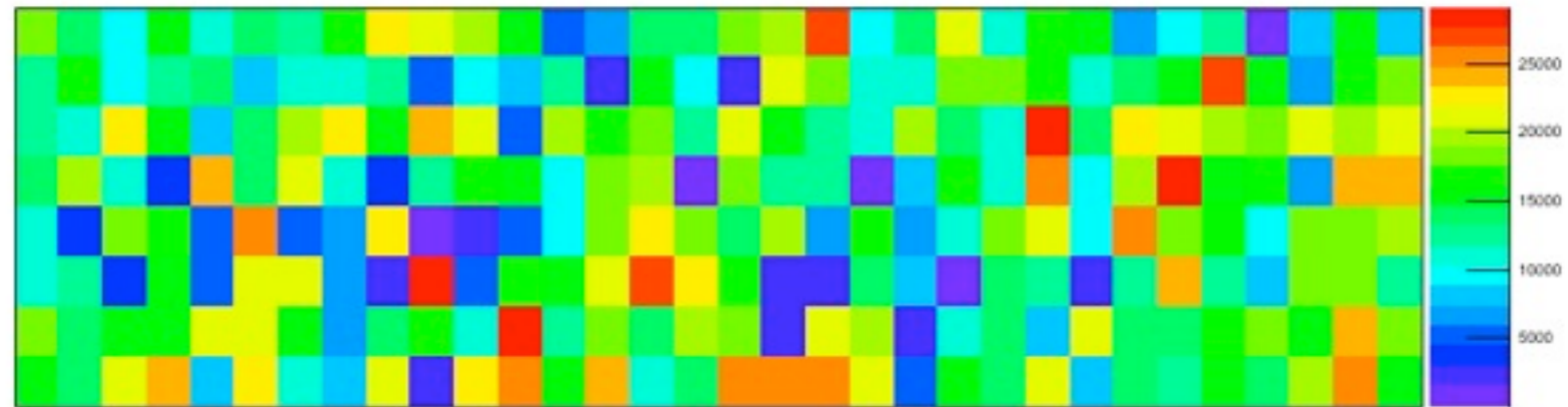


- ▶ difficult to pilot with a single threshold $\rightarrow 8 \times 32$ digital matrices *not tested on beams*

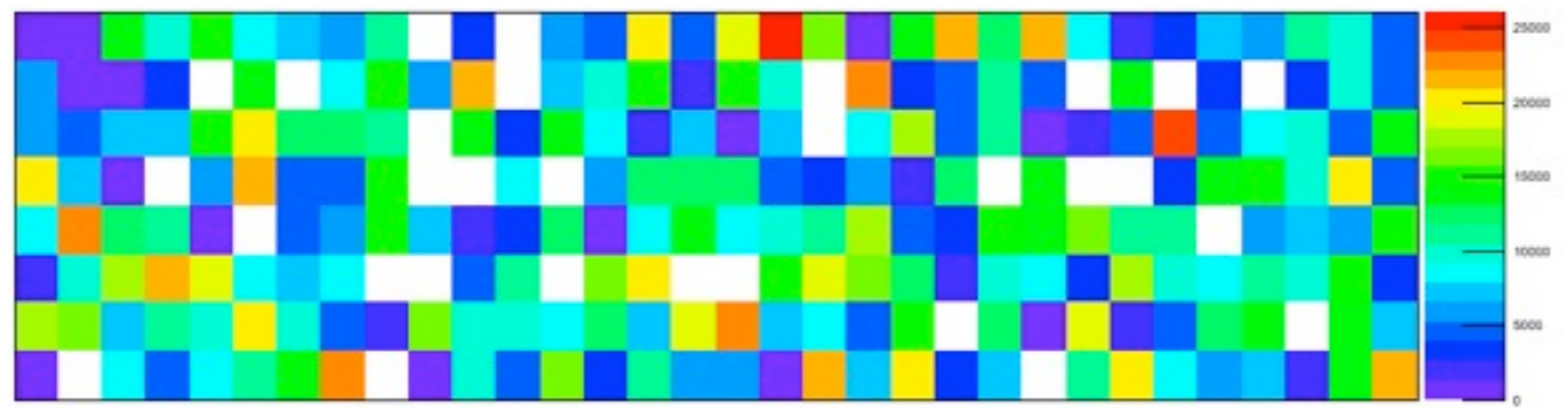
Interconnected Chips

→ response of the digital 8x32 devices to a ^{55}Fe source:

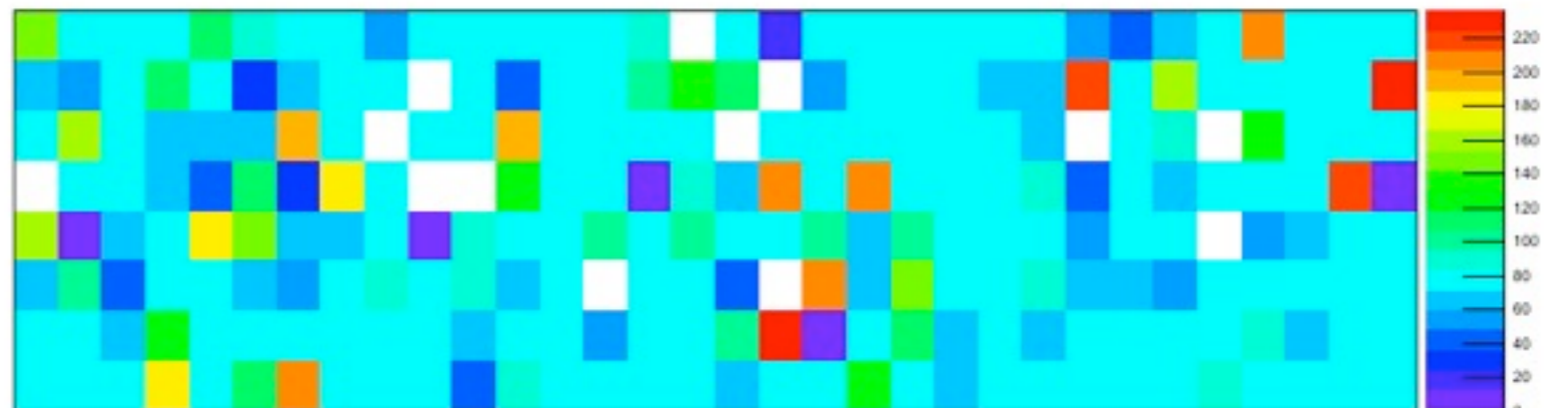
chip5:
all pixels are
interconnected!



chip6:
30 failures (12%)



chip7:
13 failures (5%)



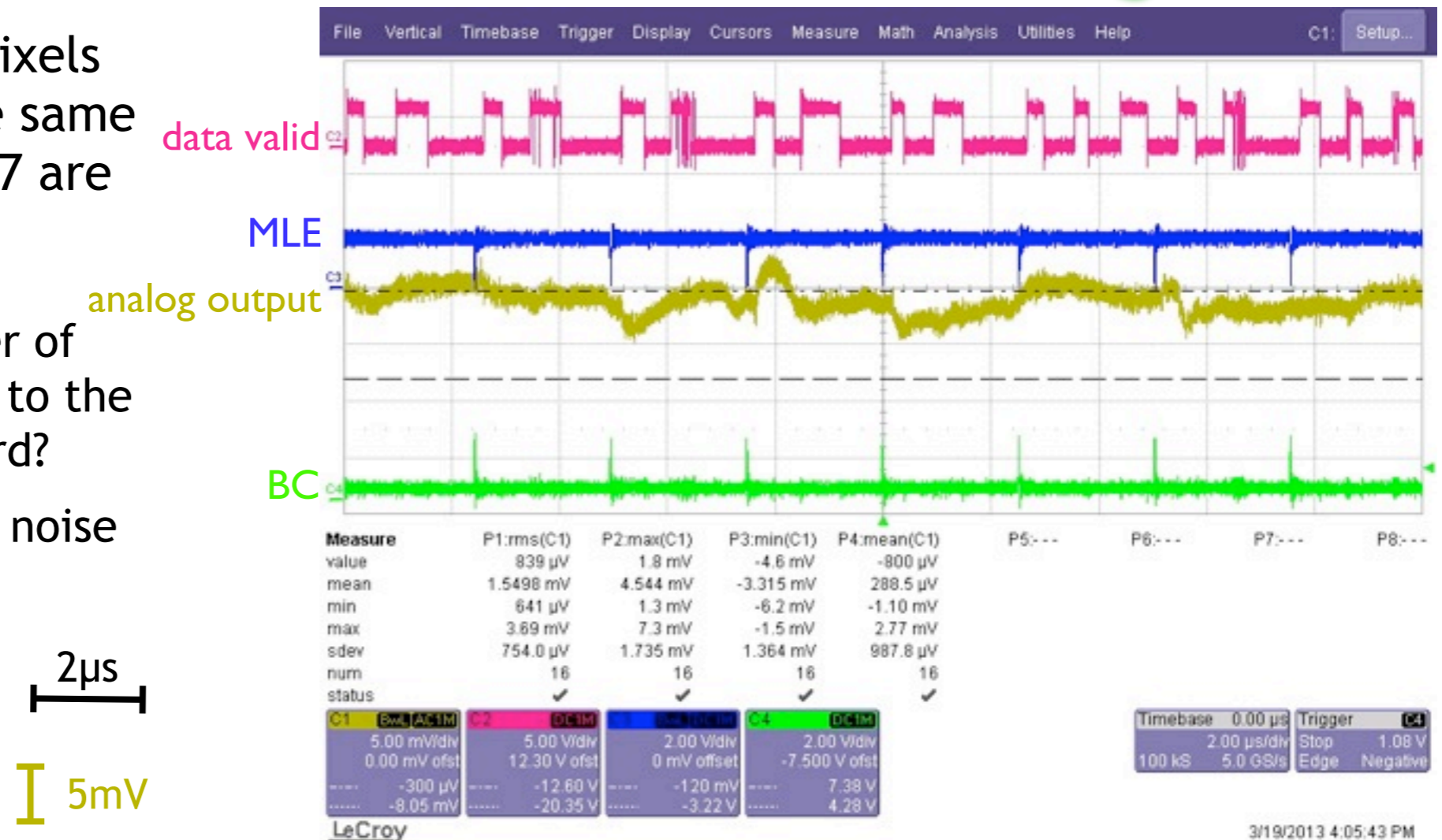
Tests on Inductions

➔ No significant inductions visible at the analog output of pixel (31,7):
tested at very high clk rates:

- rdclk = 50 MHz (20ns)
- BC \approx 2.5 μ s
- checked that pixels belonging to the same MP as pixel 31,7 are fired

- small induction, order of the noise (2 mV) due to the clk, on chip? testboard?
- 1/4 MIP (10mV) \approx 5 x noise
- safe operations

readout running:



MIP \approx 40 mV

Tests on Inductions

➔ No significant inductions visible at the analog output of pixel (31,7):
tested at very high clk rates:

- rdclk = 50 MHz (20ns)
- BC ≈ 2.5 μs
- checked that pixels belonging to the same MP as pixel 31,7 are fired

no readout:

- small induction, order of the noise (2 mV) due to the clk, on chip? testboard?
- 1/4 MIP (10mV) ≈ 5 x noise
- safe operations

2μs

5mV

MIP ≈ 40 mV



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Conclusions

→ Apse14Well:

- serious induction effects deteriorate the performance of high resistivity devices, less pronounced on low res ones
- need to understand the cause of the observed induction
- other effects (as charge sharing) may also play a role to explain the low maximum efficiency

→ Apse13D_TC:

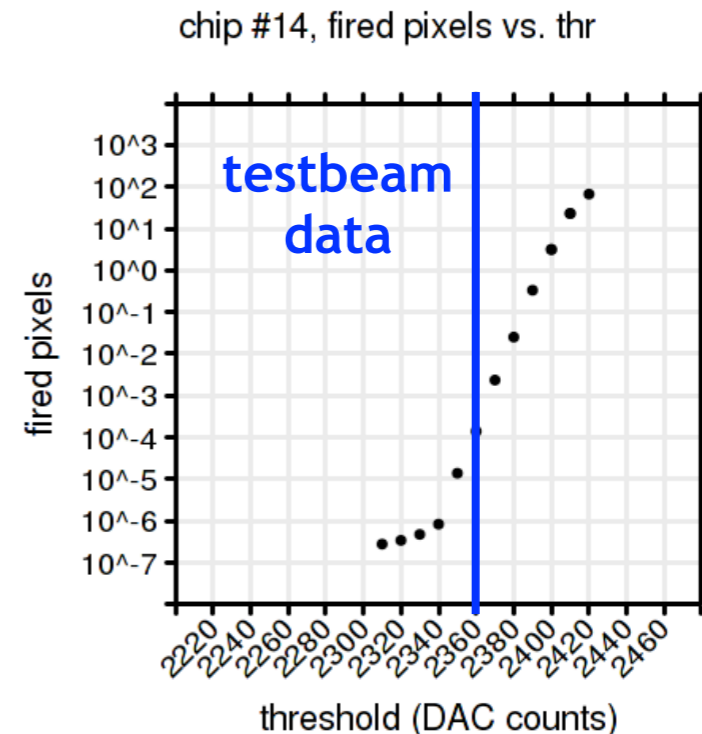
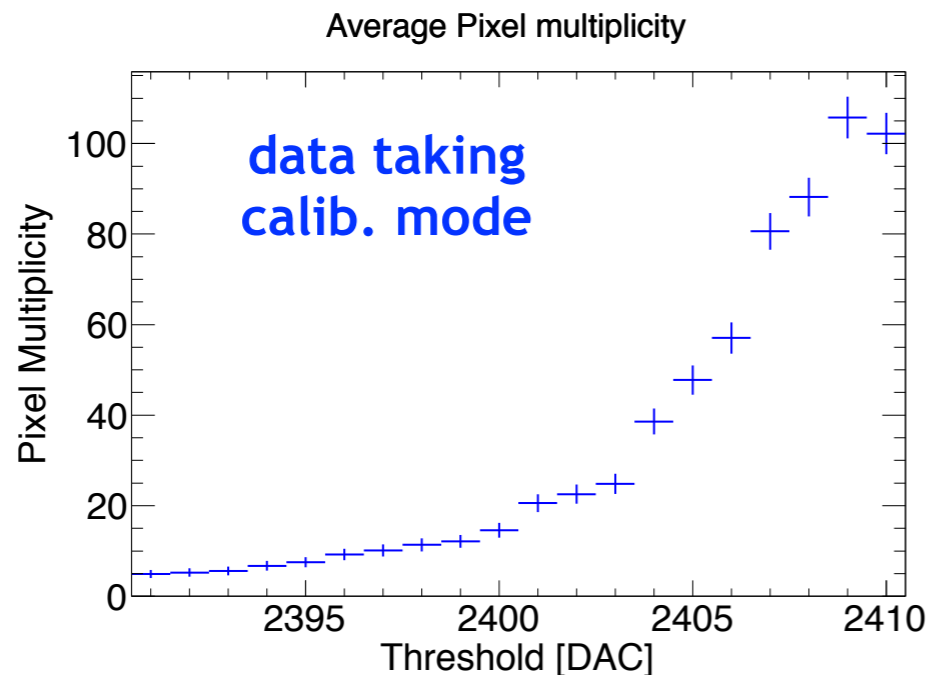
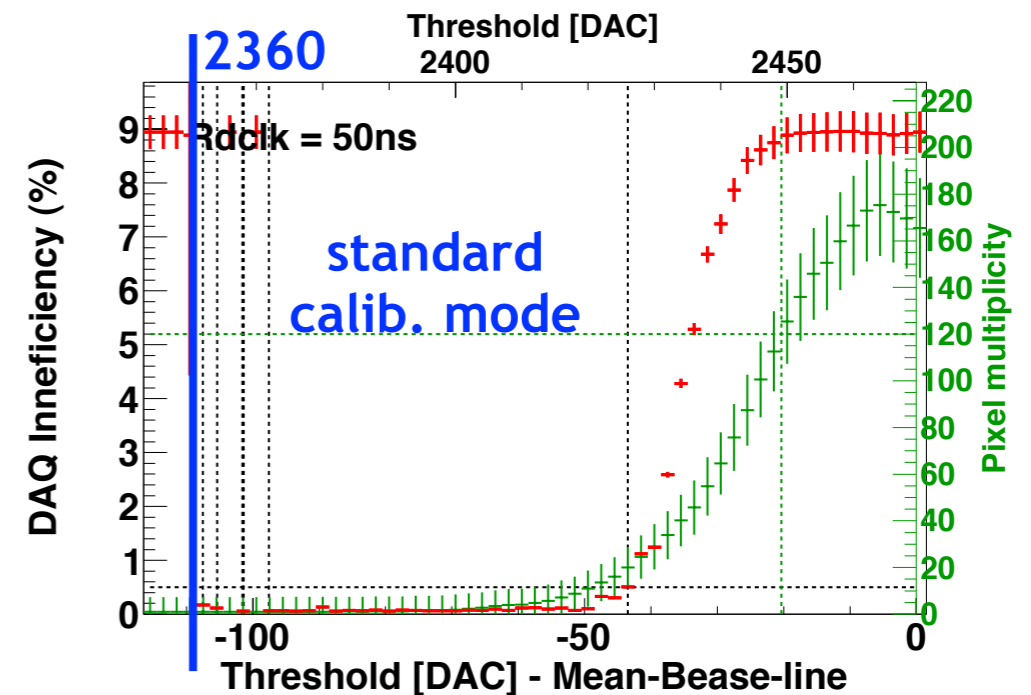
- promising results from analog devices: 98% efficiency
- 3 working interconnected chips
- large gain dispersion prevented the test with beams
- no significant induction

Additional Slides



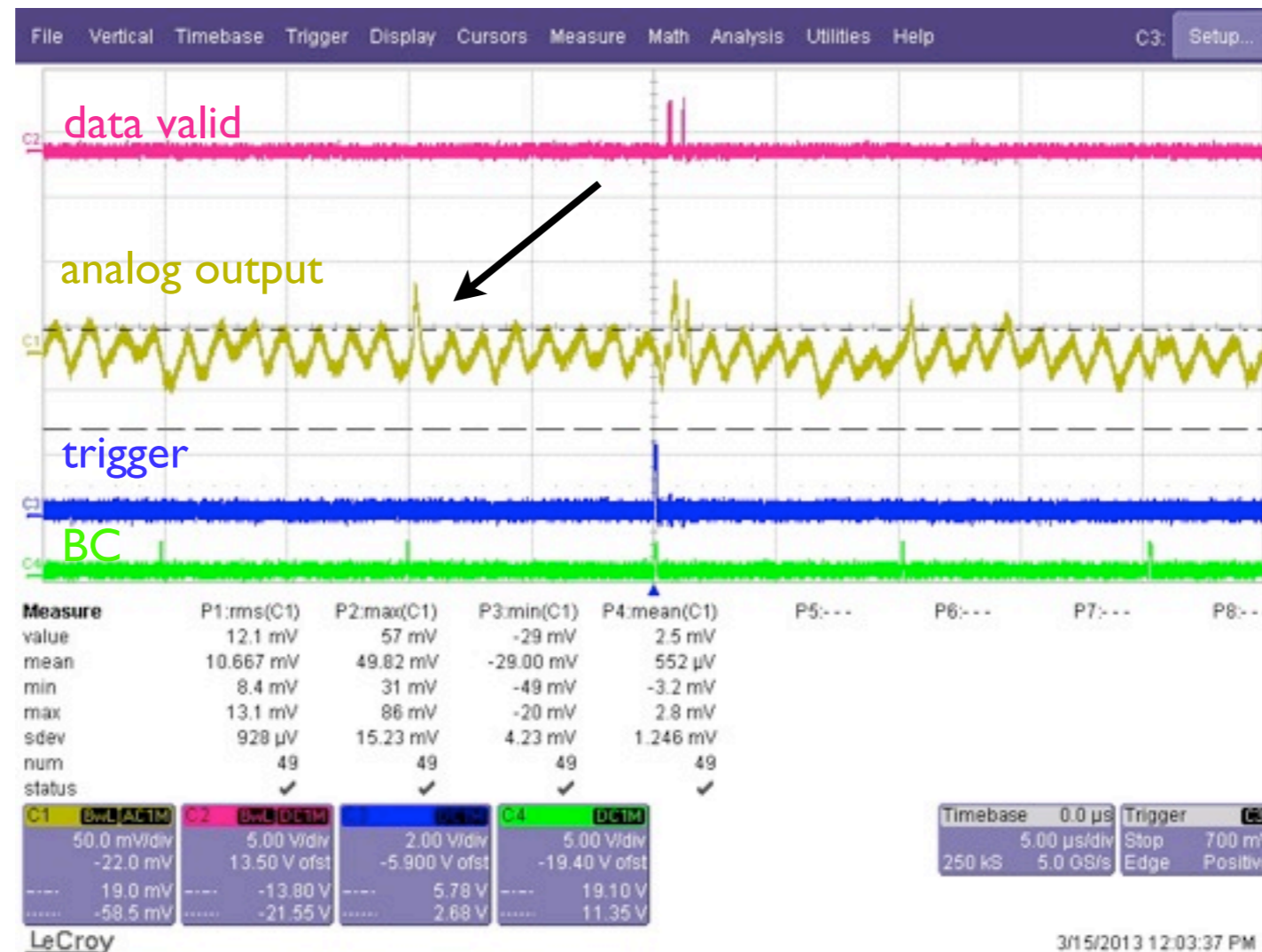
Apse14Well: Pixel Multiplicity

- ➔ pixel multiplicity in standard calibration is smaller than 1:
 - too low to cause inefficiency
 - test also in data-taking mode (pixels are enabled all the time, no observation windows)
- ➔ pixel multiplicity in data-taking mode:
 - confirm testbeam observations
 - still too low to cause observed inefficiency



Apse14Well Inductions: oscillation

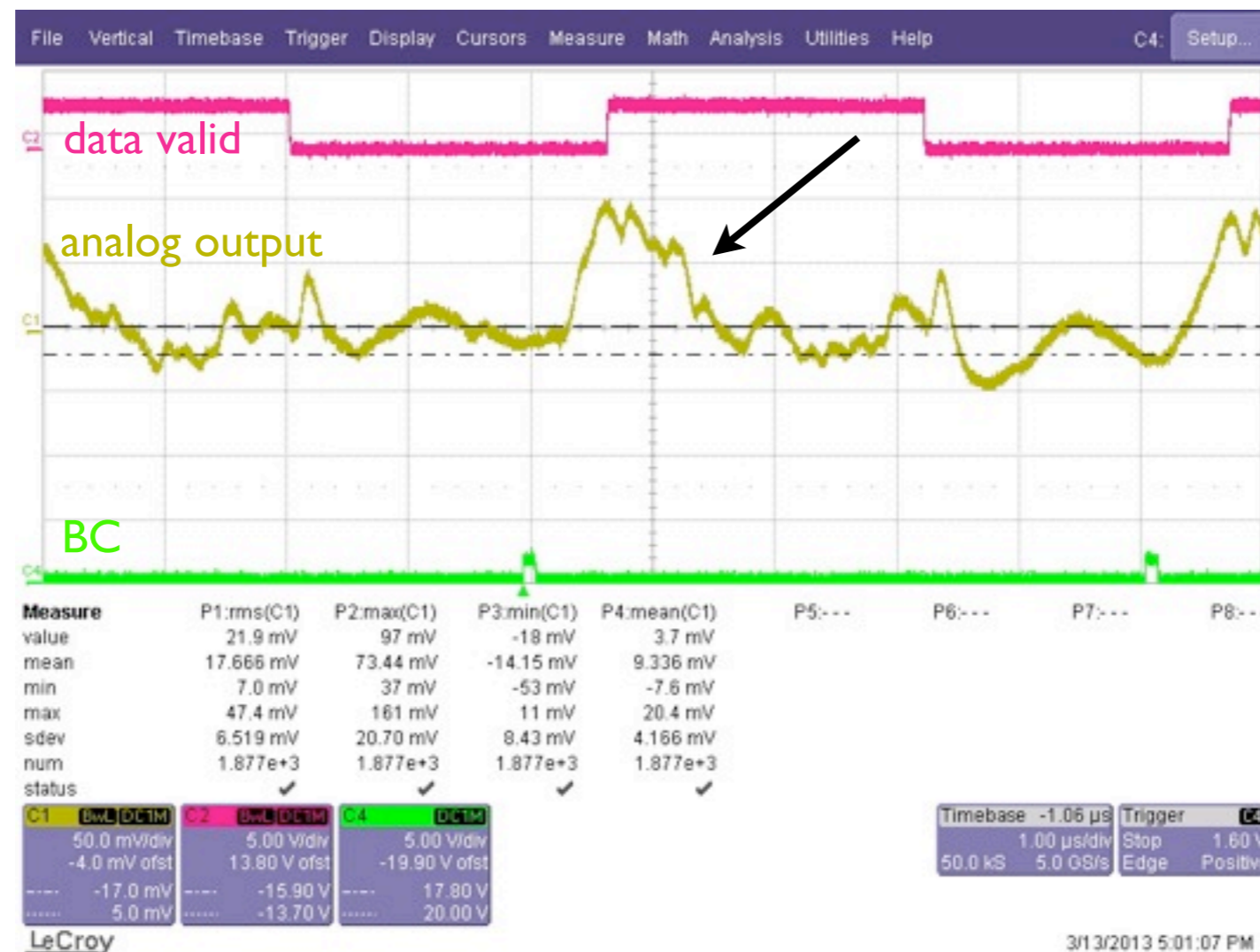
- when rdclk is fasten to 50ns, an oscillation appears
 - period $\sim 1.5\mu\text{s}$, ampl $\sim 20\text{ mV}$



note: MIP $\approx 115\text{ mV}$

data-push mode, thr \approx 2400 DAC

- positive induction ($\sim 100\text{mV}$) covers a non-negligible fraction of the time between two BCs: if a MIP hits the pixel in this time, the signal doesn't cross the threshold → inefficiency!

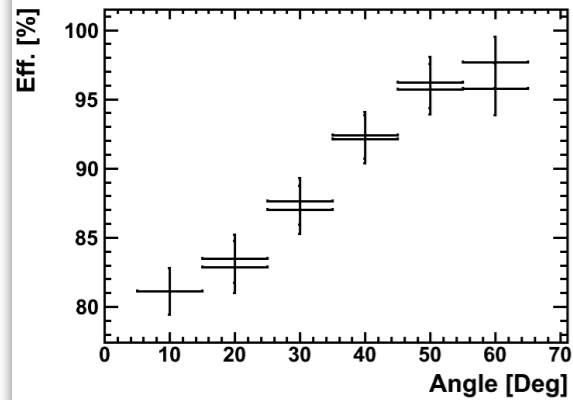


note: MIP $\approx 115\text{ mV}$

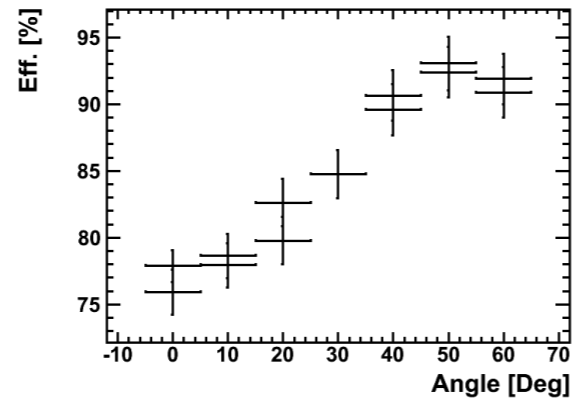
Apsel4Well: angle dependence

Eff vs. angle

CHIP 13



CHIP 14



THRESHOLD: 2360 \rightarrow $280e \pm 5\%$

presented at the SuperB
General Meeting in December

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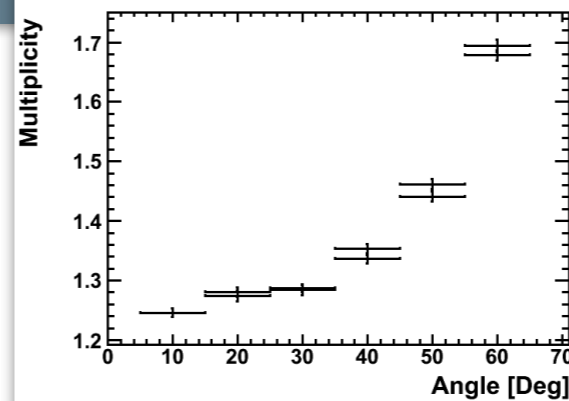
Preliminary results on INMAPS

Results

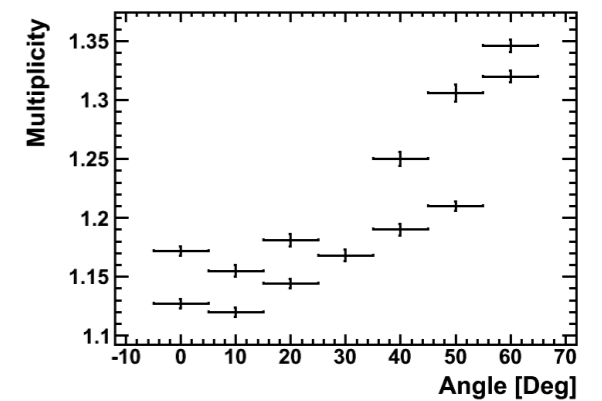
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Multiplicity vs angle

CHIP 13



CHIP 14



THRESHOLD: 2360

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Preliminary results on INMAPS

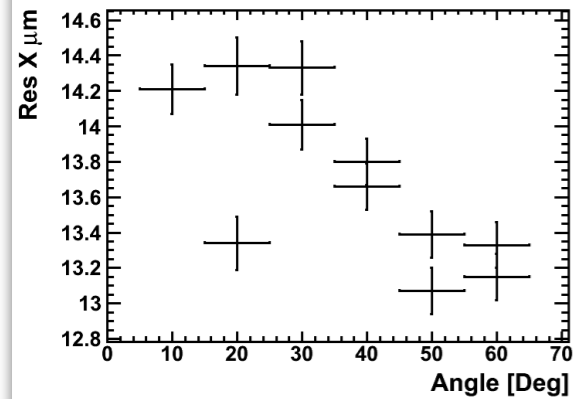
Results

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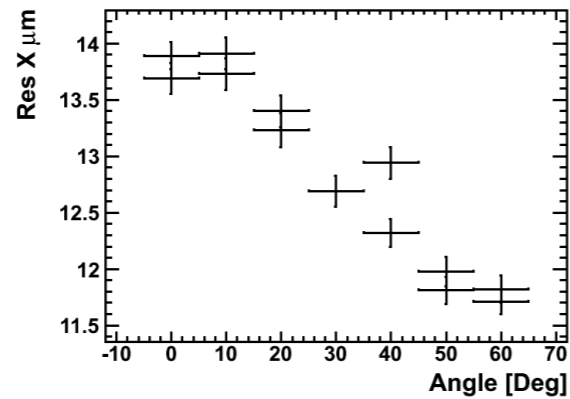
Apse4Well: resolution

Resolution X vs angle

CHIP 13



CHIP 14

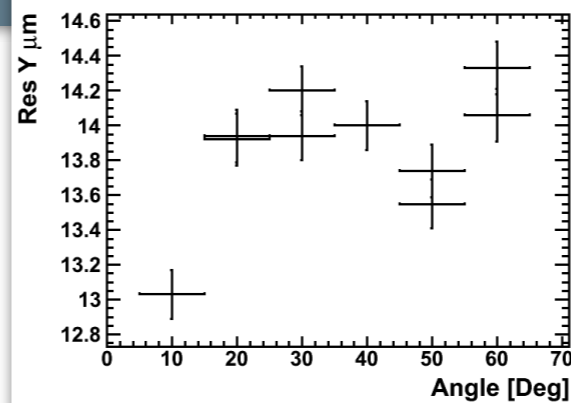


THRESHOLD: 2360

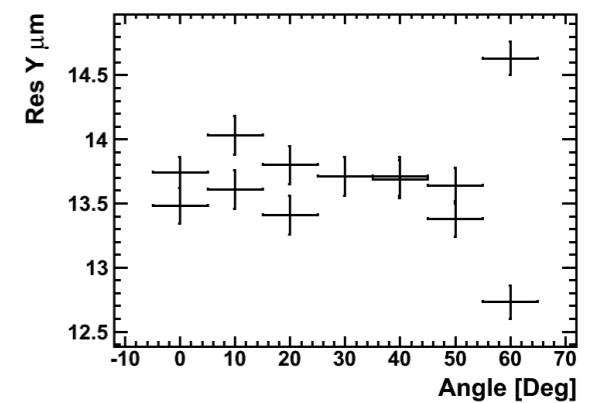
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Resolution Y vs angle

CHIP 13



CHIP 14



THRESHOLD: 2360

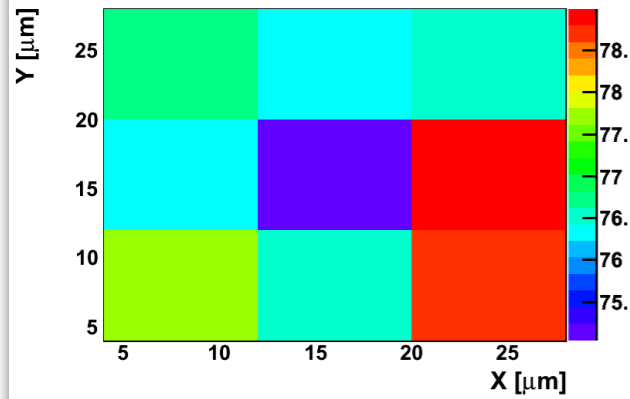
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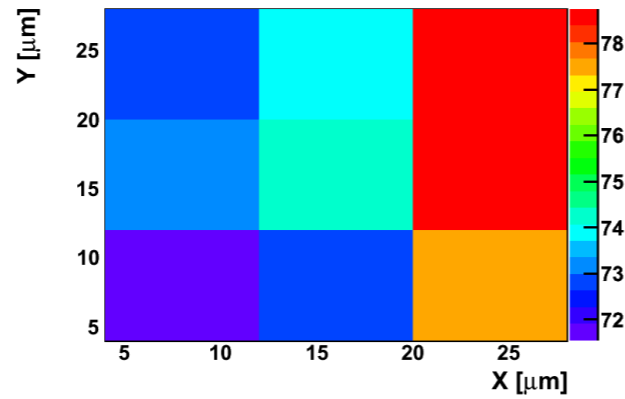
Apse14Well: lattice & pixel isotropy

Lattice isotropy

CHIP 13



CHIP 14



THRESHOLD: 2360

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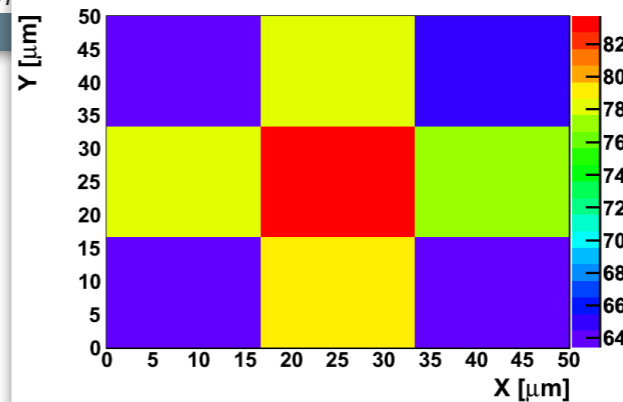
Preliminary results on INMAPS

Results

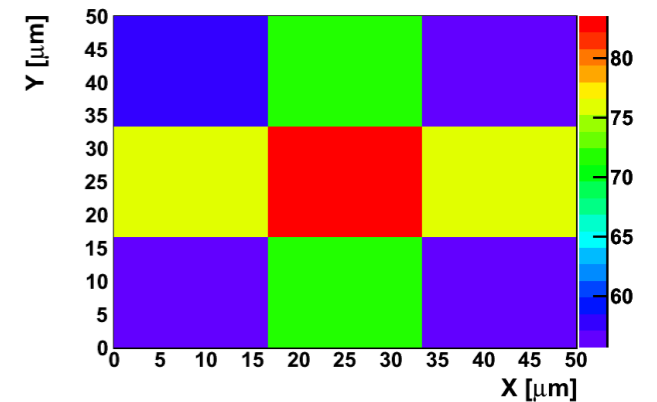
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Pixel isotropy

CHIP 13



CHIP 14



Before deconvolution the telescope resolution!

THRESHOLD: 2360

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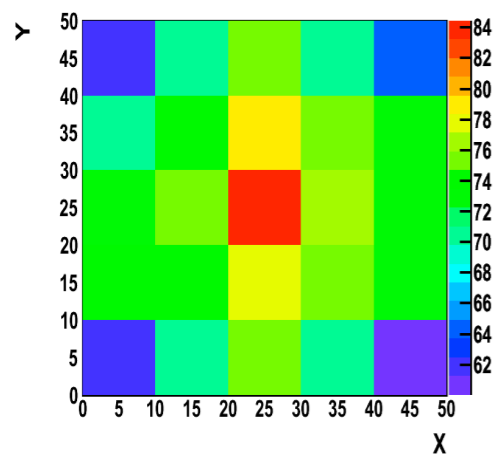
Preliminary results on INMAPS

Results

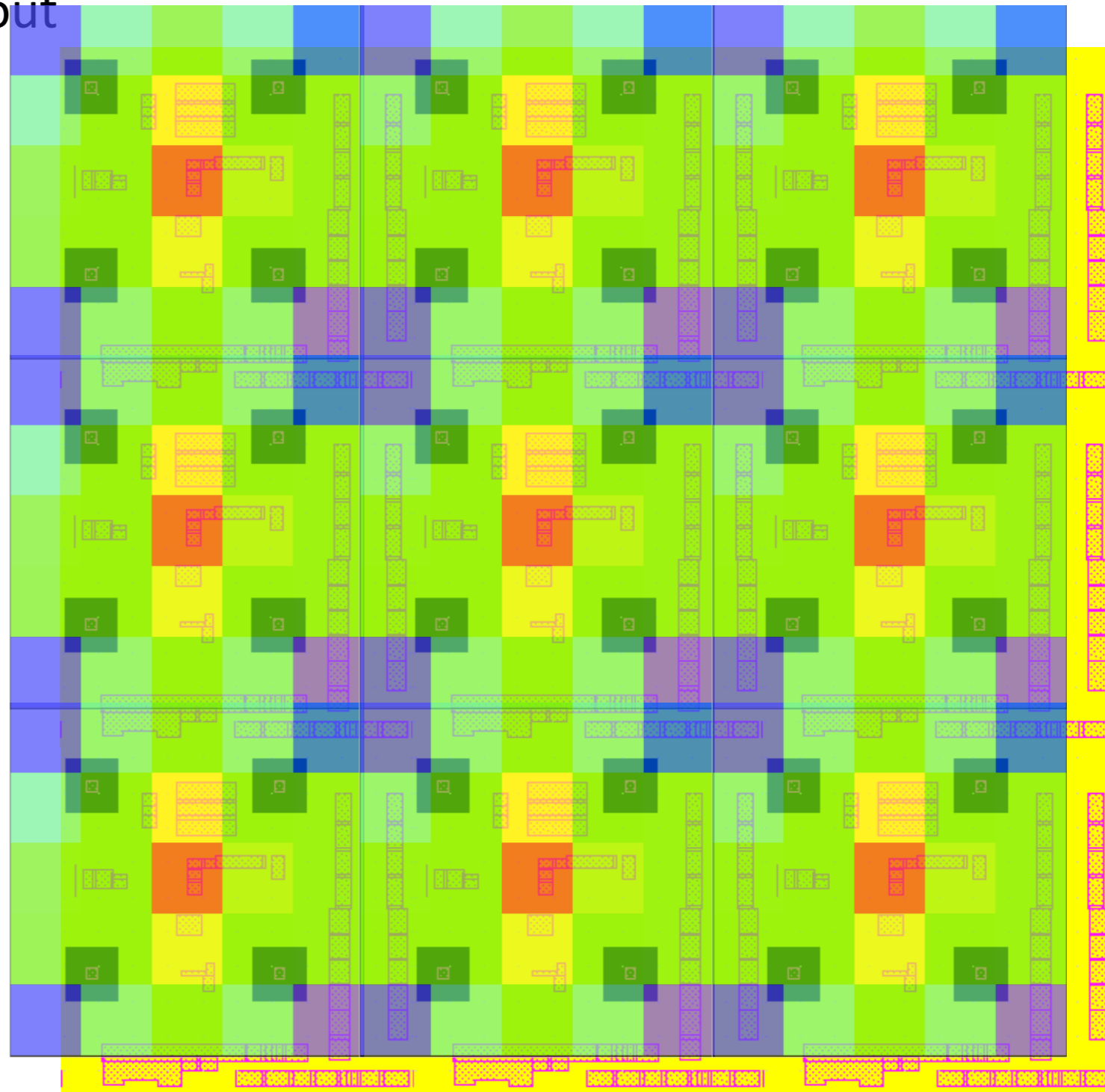
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Efficiency Within Pixel, 5x5

Apse14well pixel layout



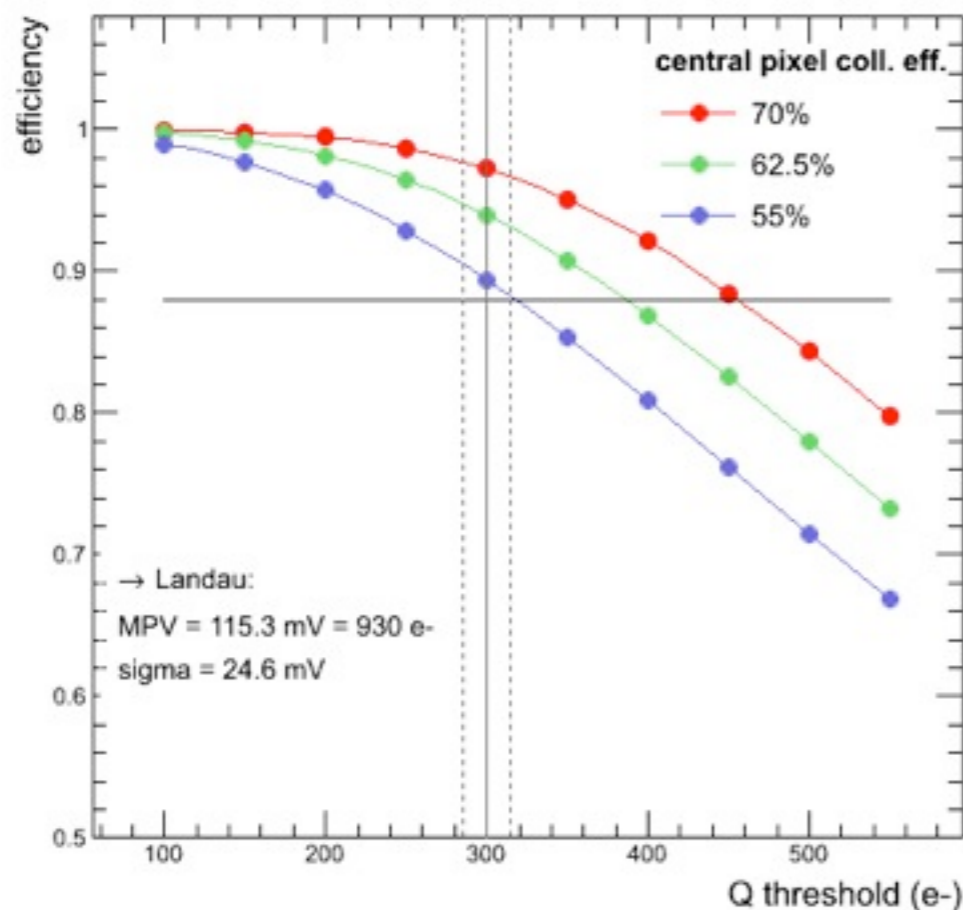
In-pixel efficiency map



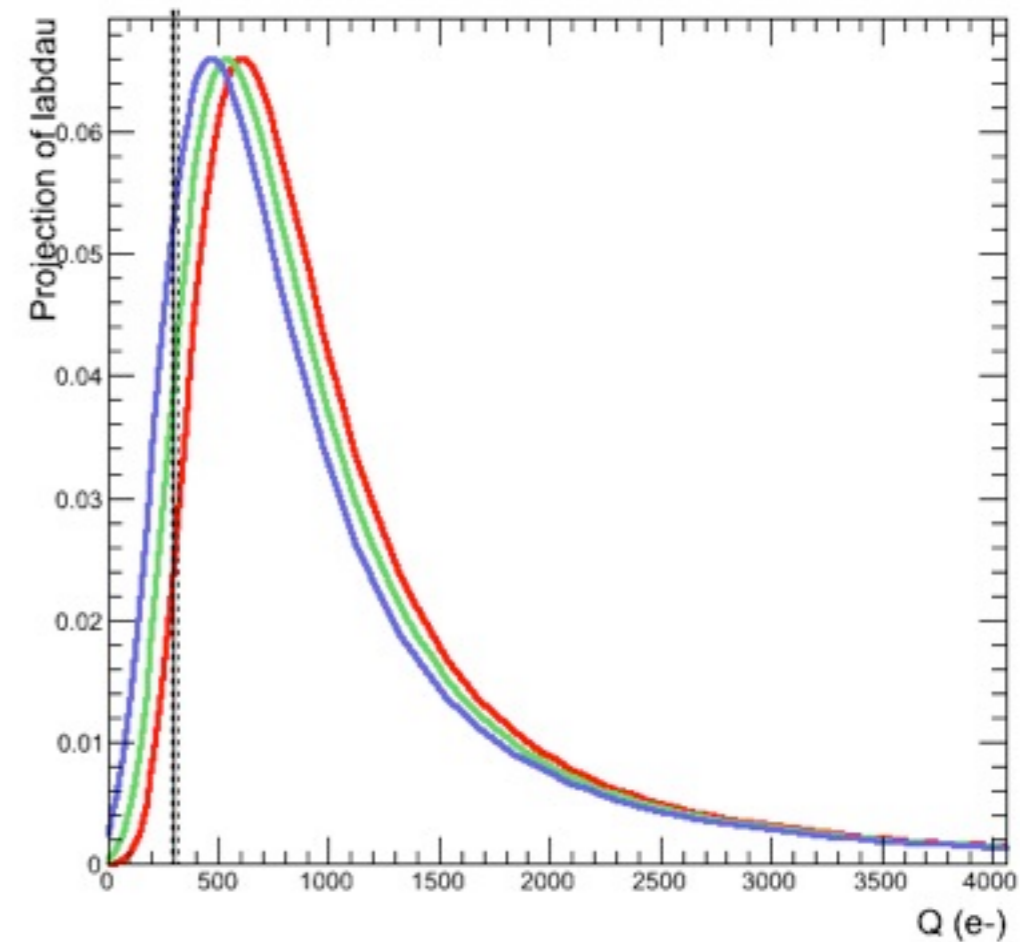
Landau from ^{90}Sr Measurements

- ➔ Landau measured with ^{90}Sr on analog devices
 - MPV = 115mV, sigma = 24.6 mV
- ➔ use gain to translate mV into e^-
- ➔ Vary the central pixel collection efficiency

Expected Sensor Efficiency - Landau



landau



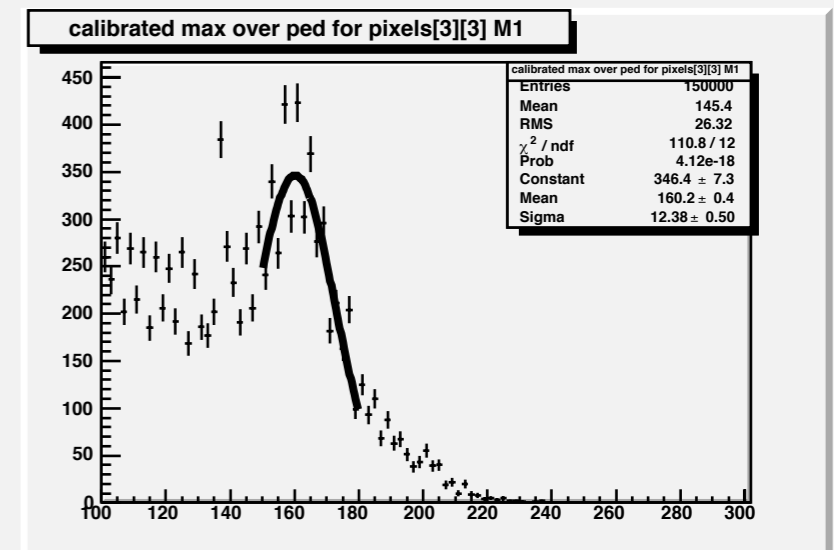
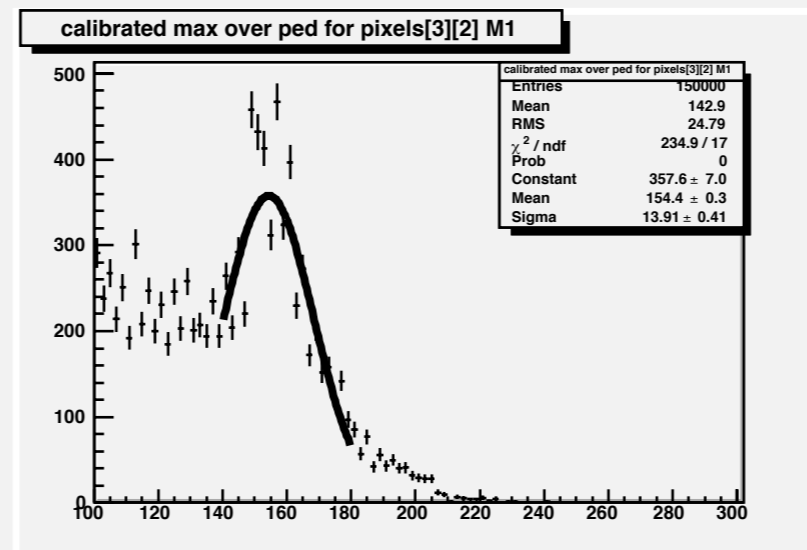
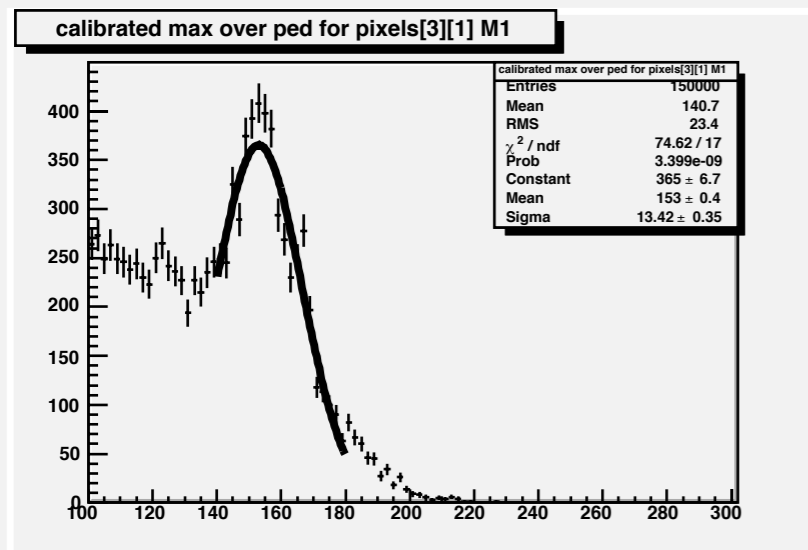
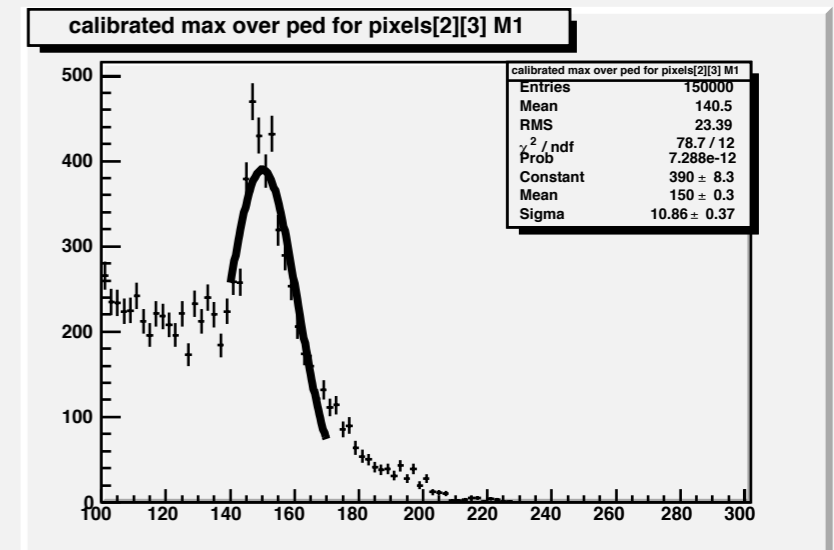
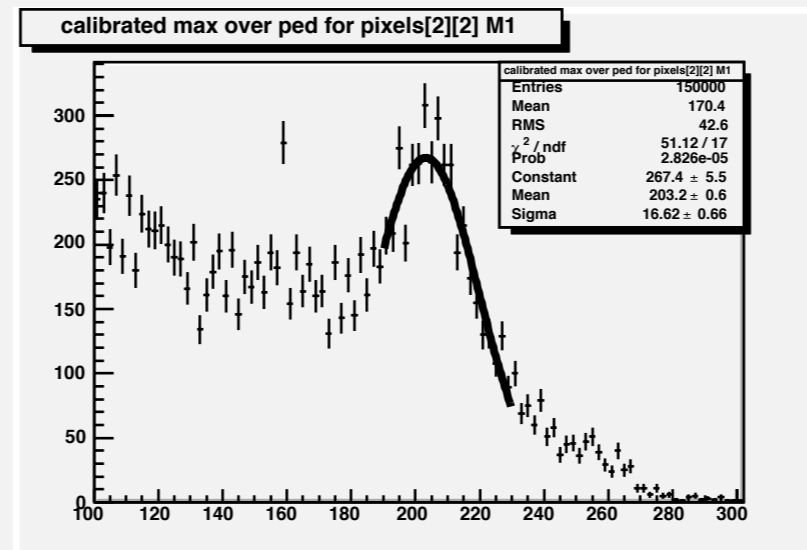
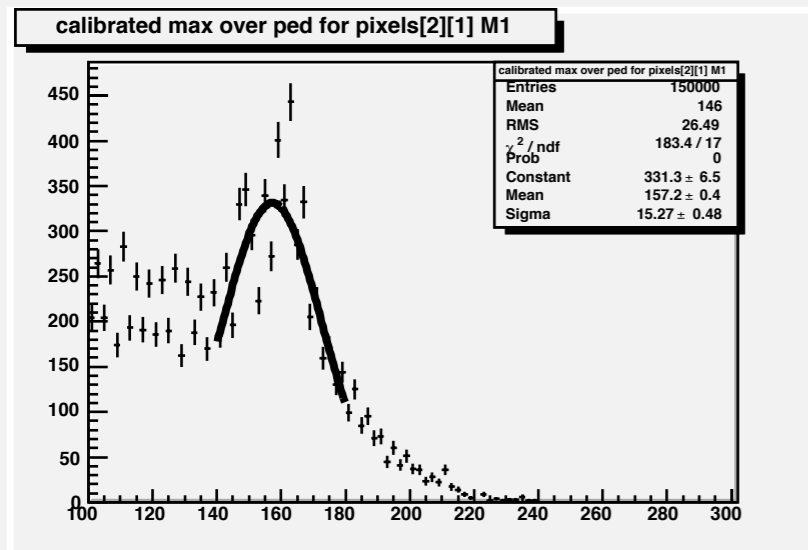
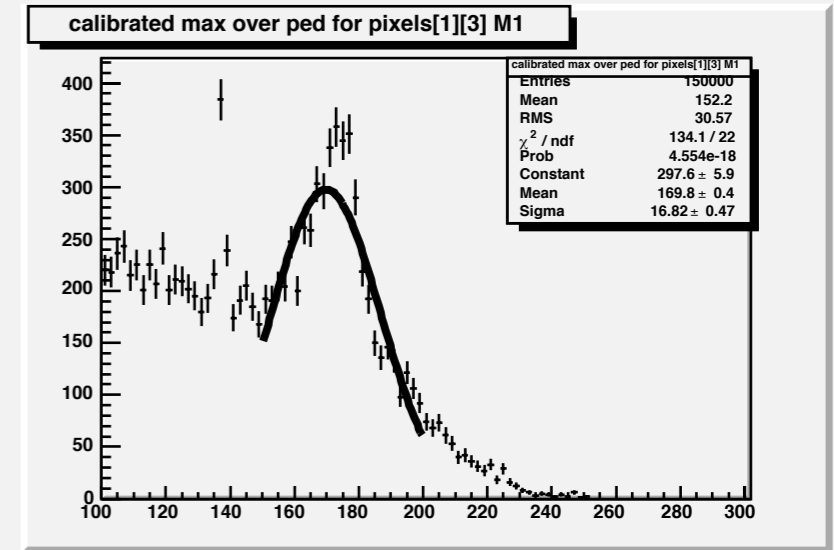
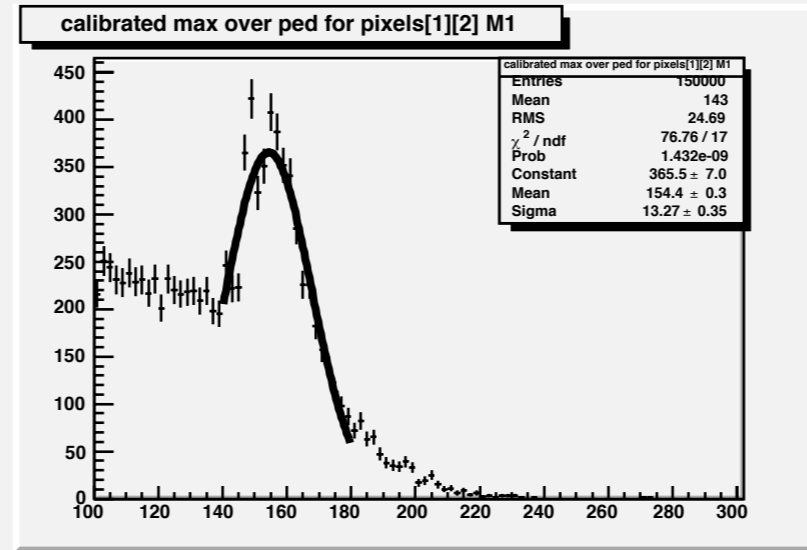
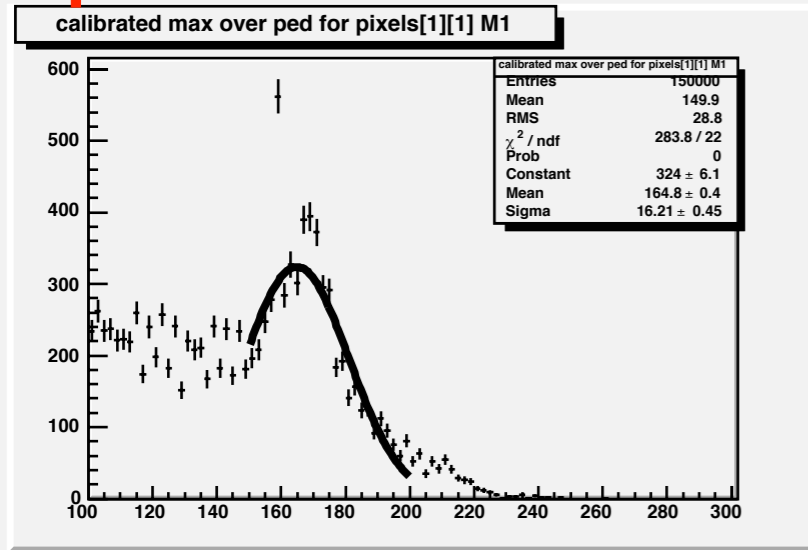
➔ central pixel collection efficiency:

▸ 70%

▸ 62.5%

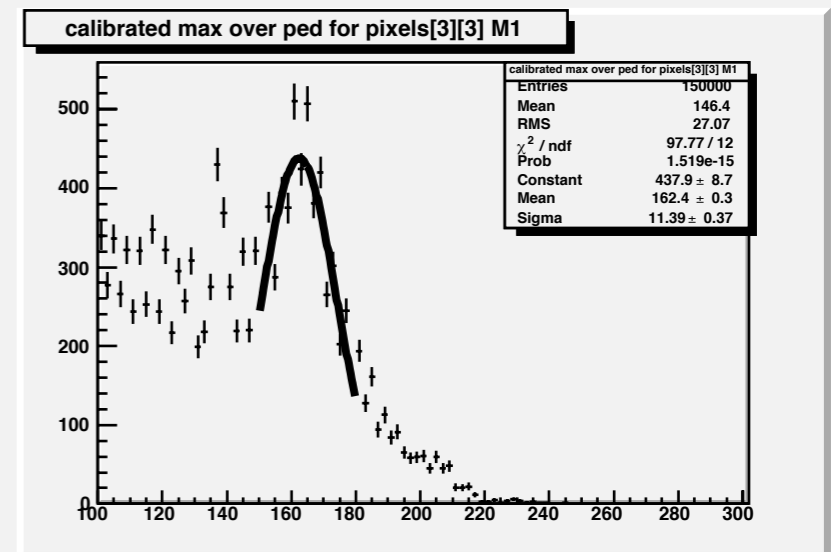
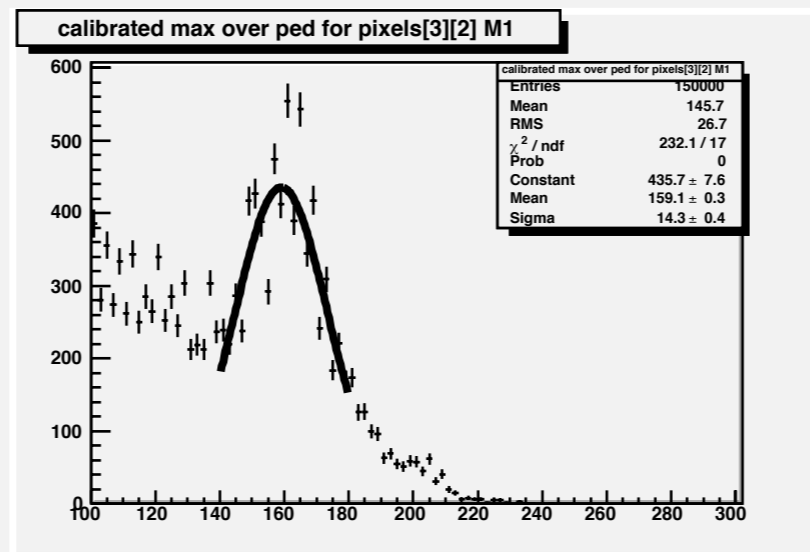
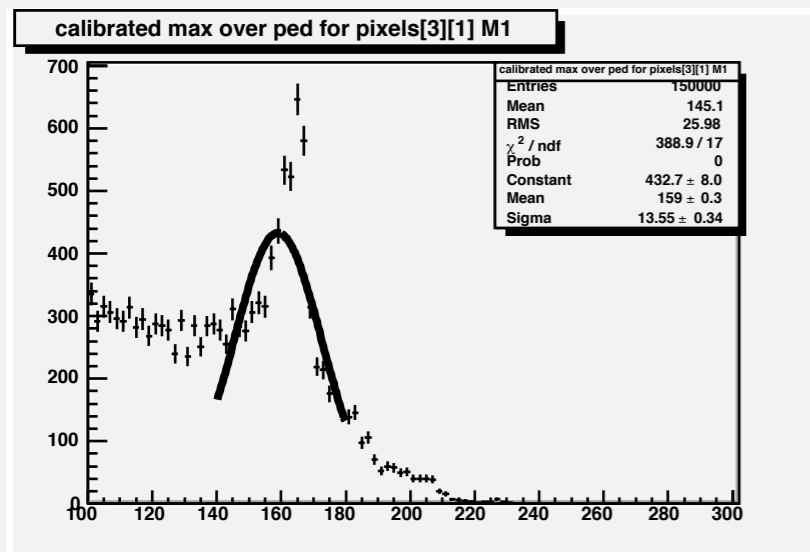
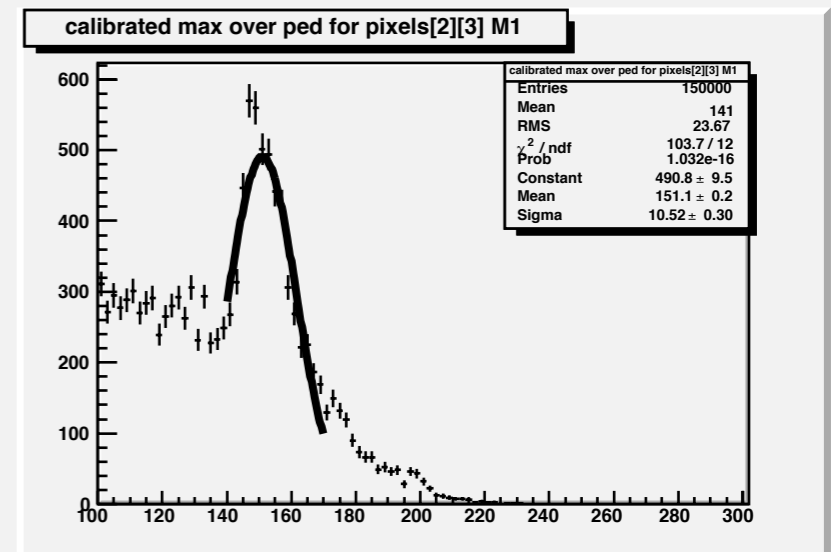
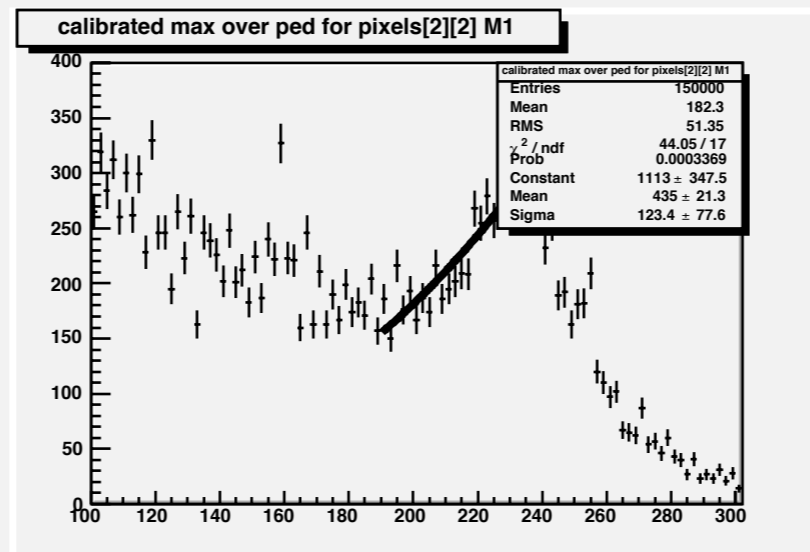
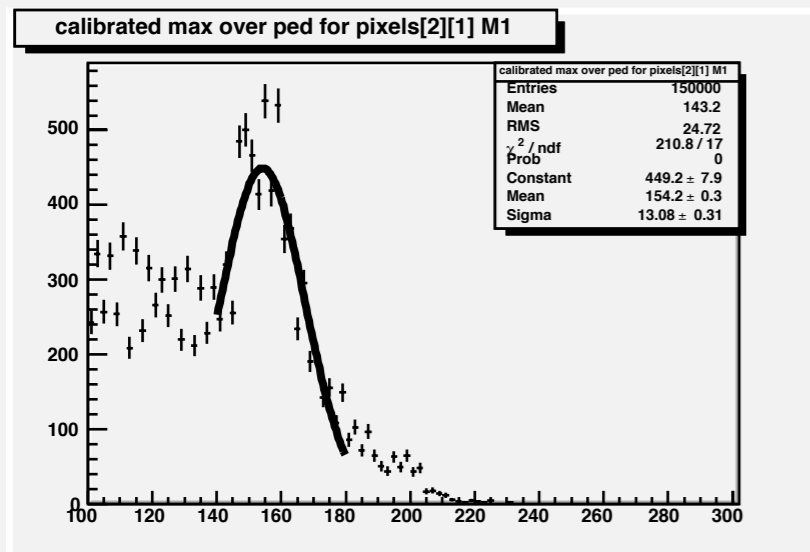
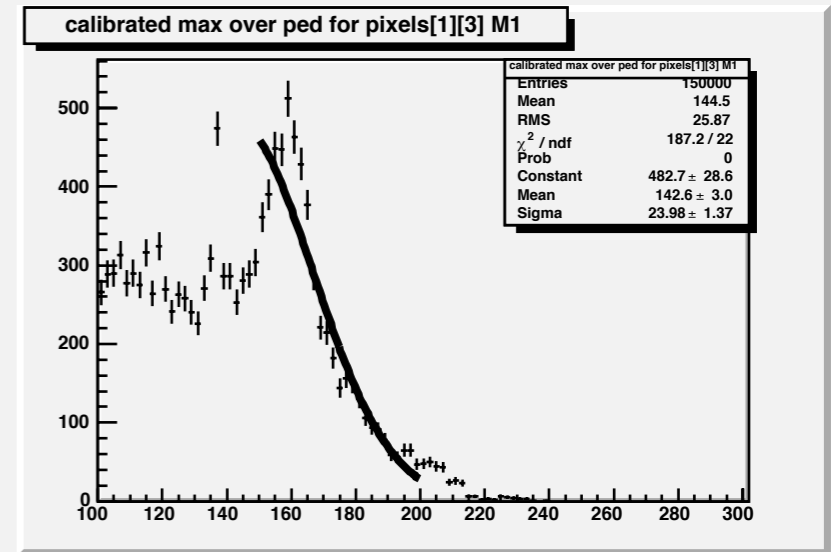
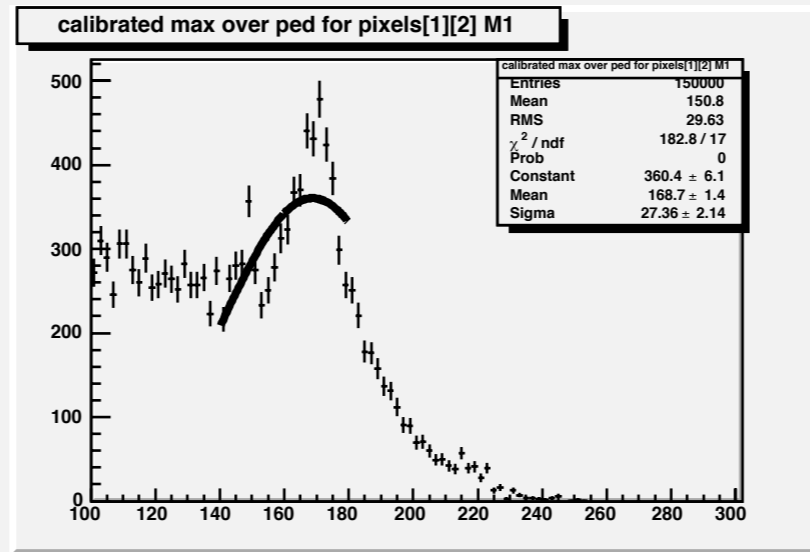
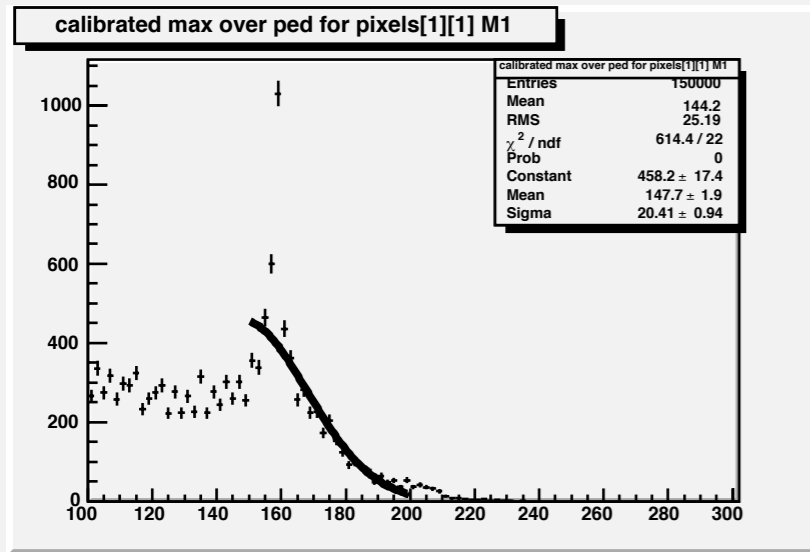
▸ 55%

Apse14Well: ^{55}Fe calibrations



Apse14Well: ^{55}Fe calibrations

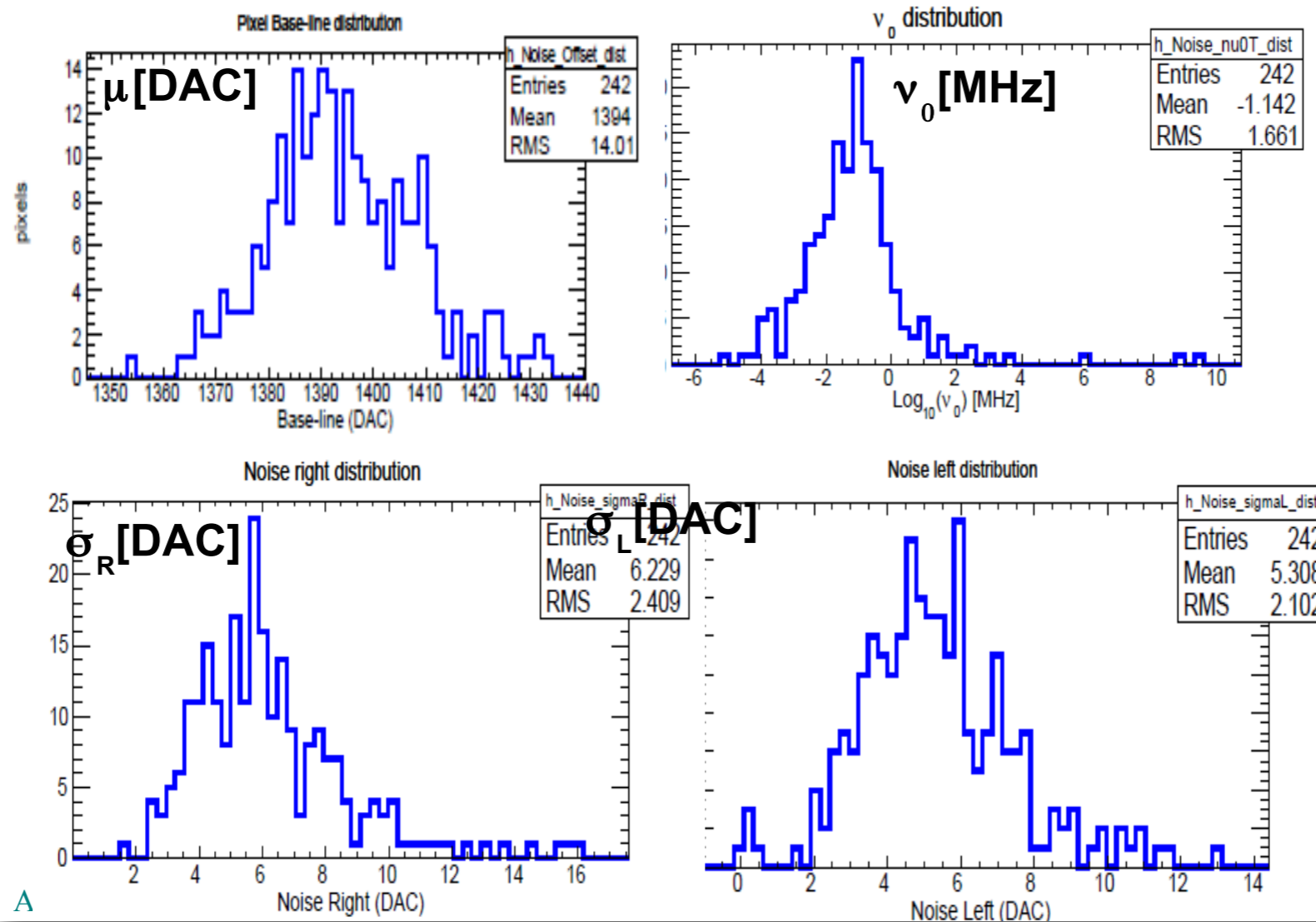
chip41



Apse13D_TC characterization

Noise scans: Chip5

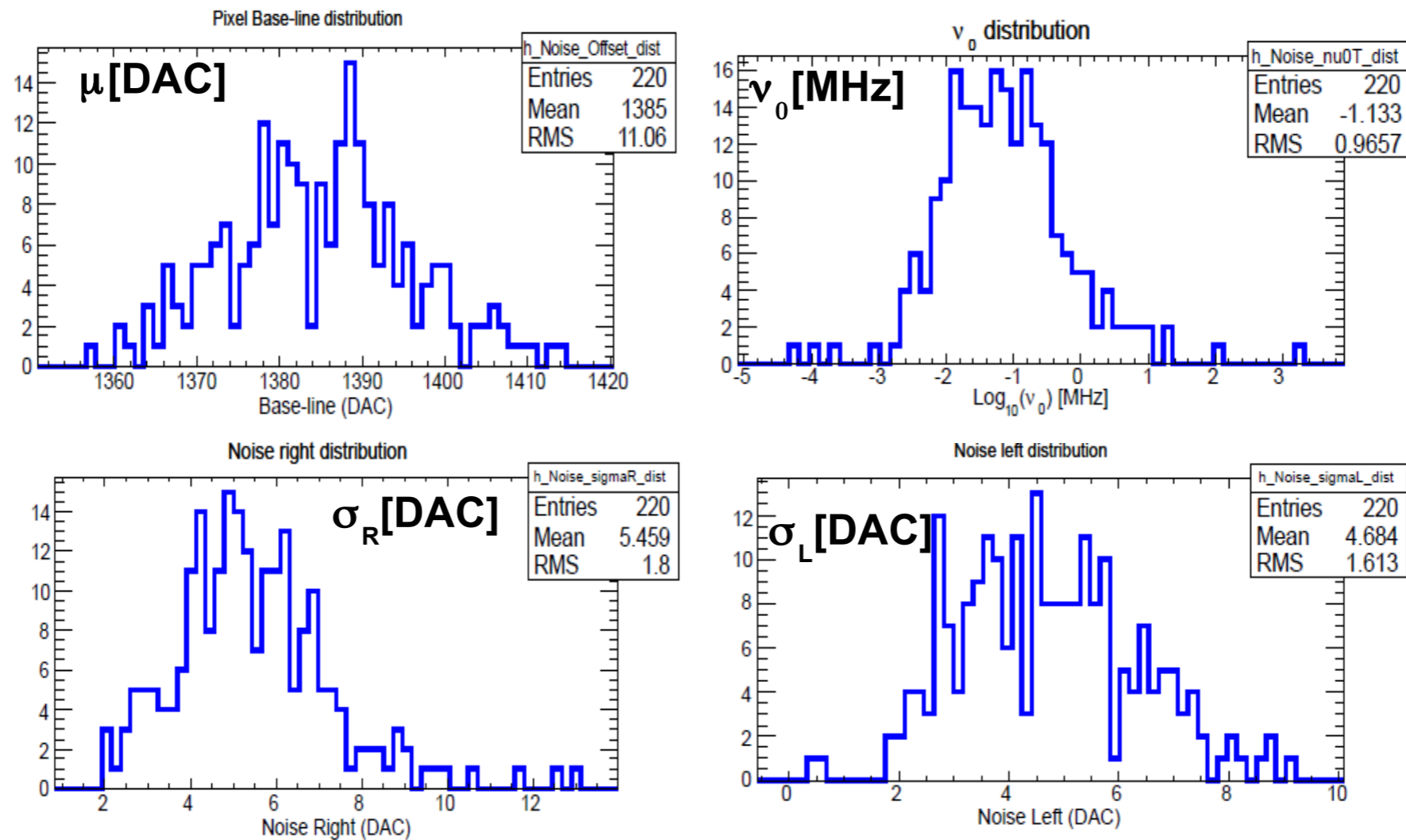
- In some cases the fit doesn't converge properly. Those pixels are not used for the plots below. 221 fits converged (there is 1 dead pixel).



Apse13D_TC characterization

Noise scans: Chip6

- In some cases the fit doesn't converge properly. Those pixels are not used for the plots below. 204 fits converged (there is 28 dead pixel).



Alejandro Pérez, LNF SuperB meeting, Dec. 12th 2012

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